FUJITSU MICROELECTRONICS PRODUCT GUIDE

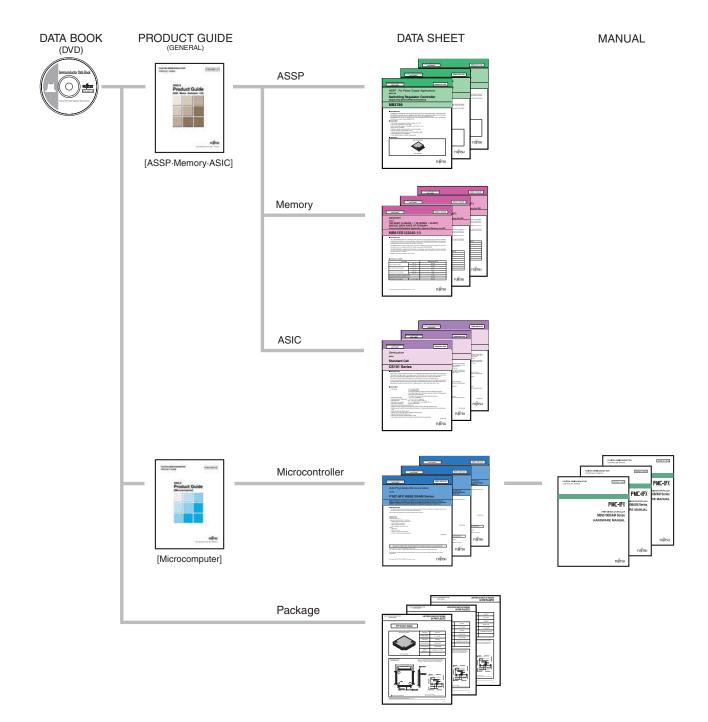
2008.1 Product Guide





THE POSSIBILITIES ARE INFINITE

Technical Documentation of Electronic Devices



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* : SPANSION [™] Products

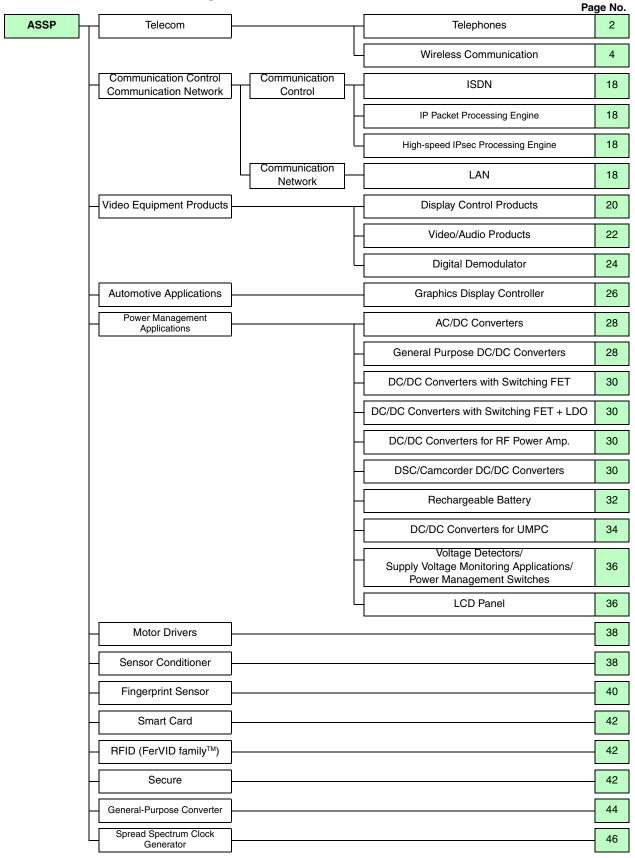
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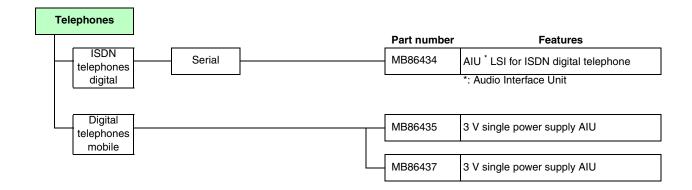
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ASSP Product Line-up

ASSP Product Line-up



Telephone Products



Telephone Products

ISDN Digital Telephone LSIs

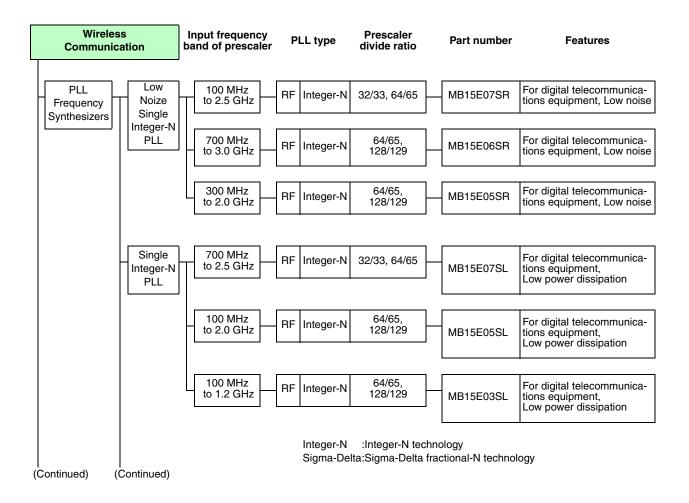
Part number	Functions	CODEC	Power supply voltage (V)	Package QFP
MB86434	AIU for ISDN digital telephones CODEC, DTMF tones, service tone Internal ringer tone	A-laW μ-laW 14-bit linear	+5±5%	64P

Package: P - Plastic

LSIs for Digital Mobile Telephones

Part number	Functions	Compression law	Power supply voltage (V)	Package LQFP
MB86435	3 V single power supply AIU	A-laW u-laW	2.7 to 3.6	64P
MB86437		linear	2.7 10 3.0	48P

Package: P - Plastic



PLL Frequency Synthesizers

Part number	Inp frequ band		PLL Type		Divide ratio			Power supply current	Power save current		ver su voltag (V)		Pac	kage
	min	max		Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	typ (μ Α)	min	typ	max	всс	TSSOF
MB15E07SR	100M	2.50		32/33,				8.0	0.1	2.7	3.75	5.0	16P	16P
MD15E075H	100101	2.50		64/65	,			7.0	0.1	2.7	3.0	5.0	TOP	IOF
MB15E06SR	700M	3.0G	Integer -N	64/65, 128/129	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	8.0	0.1	2.7	3.0	4.0	16P	16P
MB15E05SR	300M	2.00		64/65,				7.0	0.1	2.7	3.75	5.0	16P	16P
IVID 152055R	300101	2.00		128/129				6.0	0.1	2.7	3.0	5.0	10P	10P

Binary

11bit

3 to 2047

64/65,

128/129

1.2G

Single Integer-N PLL

MB15E03SL

Power supply voltage Input Power Power frequency **Divide ratio** Package supply save band (Hz) PLL (V) Part number current Туре **typ** (μ**A**) Prescal typ (mA) Program Swallow Reference min max min typ max SSOP BCC counter counter counter er Binary Binary 32/33, Binary 7bit MB15E07SL 700M 2.5G 11bit 14bit 4.5 0.1 2.4 3.0 3.6 16P 16P 64/65 0 to 127 3 to 2047 3 to 16383 Binary Binary 64/65, Binary 7bit Integer MB15E05SL 2.0G 11bit 14bit 3.5 0.1 2.4 3.0 3.6 16P 16P -N 128/129 0 to 127 3 to 2047 3 to 16383 100M

Binary 7bit

0 to 127

Binary

14bit

3 to 16383

2.5

0.1

2.4 3.0 3.6

Package: P - Plastic

16P

16P

(Continued)	(Continued)					
		Input frequency band of prescaler	PLL type	Prescaler divide ratio	Part number	Features
	Dual	400 MHz to 2.6 GHz	RF Integer-N	32/33, 64/65	MB15F78UL	For digital telecommunica- tions equipment
	Integer-N PLL	100 MHz to 1.2 GHz	IF Integer-N	16/17, 32/33		Low noise Low power dissipation
		2.0 GHz to 6.0 GHz 100 MHz	RF Integer-N	6.0G : 16/17, 32/33 1.5G : 4/5, 8/9	MB15F76UL	For digital high-speed tele- communications equipment
		to 1.5 GHz	Ű	part 4 division)		
		2.0 GHz to 4.0 GHz 200 MHz to 2.0 GHz	RF Integer-N IF Integer-N	4.0G : 64/65, 128/129 2.0G : 32/33, 64/65	MB15F74UV	Small Package For digital high-speed telecom- munications equipment
					MB15F74UL	For digital high-speed tele- communications equipment
		200 MHz to 2.25 GHz 50 MHz to 600 MHz	RF Integer-N IF Integer-N	2.25G : 64/65, 128/129 600M : 8/9, 16/ 17	MB15F73UV	Small Package For digital high-speed telecom- munications equipment
					MB15F73UL	For digital high-speed tele- communications equipment
		100 MHz to 1.3GHz 50 MHz to 350 MHz	RF Integer-N IF Integer-N	1.3G : 64/65, 128/129 350M : 8/9, 16/ 17	MB15F72UV	Small Package For digital high-speed telecom- munications equipment
					MB15F72UL	For digital high-speed tele- communications equipment
		500 MHz to 2.6 GHz	RF Integer-N	32/33, 64/65	MB15F30UV	Small Package For digital high-speed telecom-
		45 MHz to 510 MHz	IF Integer-N	8/9, 16/17		munications equipment Low power dissipation
		100 MHz to 1.1GHz 100 MHz	RF Integer-N	1.1G : 64/65, 128/129 1.1G : 64/65,	MB15F07SL	For digital high-speed telecom- munications equipment Low noise
		to 1.1GHz	Integer-N	128/129 :Integer-N tec Ita:Sigma-Delta	0,	logy

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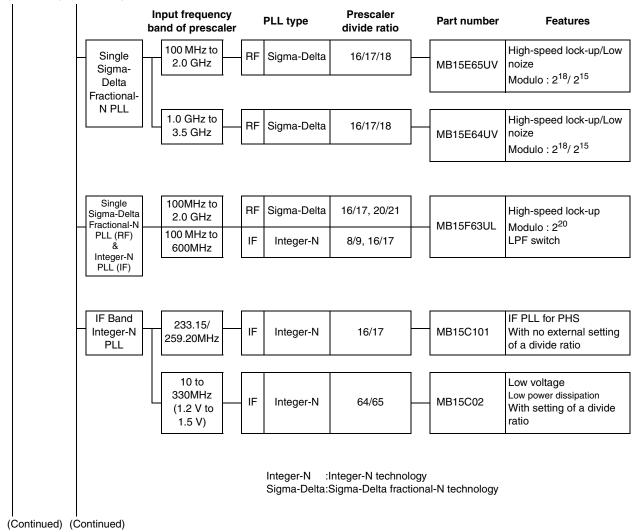
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Dual Integer-N PLL

Part number	frequ	out iency (Hz)	PLL		Divide ra	itio		Power supply current	Power save current	v	er su oltag (V)		Pac	kage
	min	max	Туре	Prescaler	Program counter	Swallow counter	Referenc e counter	typ (mA)	typ (μ Α)	min	typ	max	всс	TSSOP
MB15F74UV	2.0G 200M	4.0G 2.0G		RF : 64/65, 128/129 IF : 32/33, 64/65	Binary	Dinom	Binary	6.5 2.5	0.1 0.1	2.7	3.0	3.6	18P	_
MB15F73UV	200M 50M	2.25G 600M		RF:64/65, 128/129 IF:8/9, 16/17	11 bit 3 to	Binary 7bit 0 to 127	14bit 3 to	2.0 1.2	0.1 0.1	2.4	2.7	3.6	18P	-
MB15F72UV	100M 50M	1.3G 350M		RF : 64/65, 128/129 IF : 8/9, 16/17	2047	0 10 121	16383	1.5 1.0	0.1 0.1	2.4	2.7	3.6	18P	-
MB15F30UV	500M 45M	2.6G 510M		RF : 32/33, 64/65 IF : 8/9, 16/17	Binary 11 bit 3 to 2047	Binary 7bit 0 to 63	Binary 15bit 3 to 32768	2.8 1.2	0.1 0.1	2.4	2.7	3.6	18P	_
MB15F78UL	400M 100M	1.2G	Integer	RX : 32/33, 64/65 TX : 16/17, 32/33	Binary 11 bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	2.8 1.7	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F76UL	2.0G 100M	6.0G 1.5G	-N	RF : 16/17, 32/33 (Fixed part 4 division) IF : 4/5, 8/9 (Fixed part 4 division)	1301	Binary 5bit 0 to 31	Binary 14bit 3 to 16383	6.2 2.3	0.1 0.1	2.5	3.0	3.6	20P	_
MB15F74UL	2.0G 200M	4.0G 2.0G		RF : 64/65,128/129 IF : 32/33,64/65		Discourse	Binary	6.5 2.5	0.1 0.1	2.7	3.0	3.6	20P	-
MB15F73UL	200M 50M	2.25G 600M		RF : 64/65,128/129 IF : 8/9,16/17	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	14bit 3 to	2.0 1.2	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F72UL	100M 50M	1.3G 350M		RF : 64/65,128/129 IF : 350M: 8/9,16/17		0 10 127	16383	1.5 1.0	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F07SL	100M 100M			64/65,128/129 64/65,128/129	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	5.5 5.5	0.1 0.1	2.5	3.0	3.6	16P	16P

Package: P - Plastic

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Single Sigma-Delta Fractional-N PLL

Part number	Inp frequ band		PLL Type		Divide	ratio		Power supply current typ	supply current typ	supply current typ	PowerPowersupplysavecurrentcurrent		ver su voltag (V)	ipply je	Pack age
	min	max	Type	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	typ (μΑ)	min	typ	max	всс		
MB15E65UV	100 M		Sigma-	16/17/18	Binary 8 bit 9 to 255	Binary 4 bit 0 to 15	Binary 6 bit 1 to 63	4.6	0.1	2.7	3.0	3.3	18P		
MB15E64UV	1.0 G	3.5 G	Delta	16/17/18	Binary 8 bit 9 to 255	Binary 4 bit 0 to 15	Binary 6 bit 1 to 63	4.6	0.1	2.7	3.0	3.3	18P		

Package: P - Plastic

• Single Sigma-Delta Fractional-N PLL (RF) & Integer-N PLL (IF)

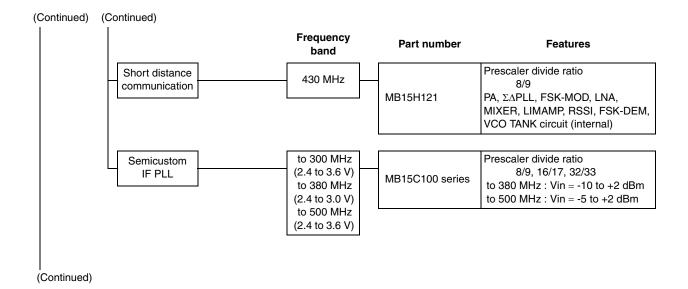
Part number	frequ	out iency (Hz)	PLL Type		Divid	e ratio		Power supply current		s	Powe supp tage	ly	Pack age
	min	max	туре	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	typ (μ Α)	min	typ	max	всс
MB15F63UL			Sigma -Delta, Integer -N	RF : 16/17, 20/21,	Binary 7bit 5 to 127(RF) Binary 11bit 3 to 2047(IF)	Binary 7hit	Binary	6.1 1.4	0.1 0.1	2.7	3.0	3.3	20P

Package: P - Plastic

• IF Band Integer-N PLL

Part number	Inp frequ band	ency	PLL Type		Divid	e ratio			save	Power supp voltage (V			Package
	min max			Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	typ (μ Α)	min	typ	max	TSSOP
MB15C101	233 259	-	Integer- N	16/17	291 33	7 12	384 40	1.0	_	2.4	3.0	3.6	8P
MB15C02	10 M	330M	Integer- N	64/65	12bit, 5 to 4095	6bit, 0 to 63	14bit, 16 to 16383	1.0	70	1.0	1.2	1.5	16P 20P

Package: P - Plastic



Specific power saving communication

Part number	Application	Frequency band	Functions	Power supply current	Power save current		er su tage	pply (V)	Package	
		(MHz)		typ (mA)	typ (μA)	min	typ	max	LQFP	
MB15H121	Telemeter telecontroller security	430	Prescaler divide ratio 8/9 PA, ΣΔPLL, FSK-MOD, LNA, MIXER, LIMAMP, RSSI, FSK-DEM, VCO TANK circuit (internal)	6.7 (PLL) 23.0 (TX) 5.0 (RX)	0.3	2.2	2.5	2.8	48P	

Package: P - Plastic

Semicustom IF PLL

		Frequency		Power	Comparison	Swallow	Reference	Power	Pac	kage
Part num (Series na		Frequency band (MHz)	Prescaler divide ratio	supply current (mA)	main counter divide ratio (N)	counter divide ratio (A)	counter divide ratio (R)	supply	SSOP	BCC
MB15C10 series	00	to 300 * ¹ (2.4 to 3.6 V) to 380 * ¹ (2.4 to 3.0 V) to 500 * ² (2.4 to 3.6 V)	8/9, 16/17, 32/33	1.2 (300 MHz, V _{CC} = 3 V)	Any value between divide-by-5 and divide- by-4095	Any value between divide-by-0 and divide- by-31	Any value between divide-by-5 and divide- by-4095	+2.4 to +3.6	8P	16P (S type)

*1: Input sensitivity –10 to +2 dBm *2: Input sensitivity –5 to +2 dBm

Package: P - Plastic

(Continued) Application Part number Features CDMA, GSM, Compact type with wide variable frequency Single Type VCO * VC-90 series PCS, PHS band (700 MHz to 2500 MHz) Ultra Compact type with wide variable fre-V10x series quency band CDMA. PCS. Compact dual band type with band selection Dual Type V08 series GSM function (800 MHz to 2500 MHz) Compact dual band type with band selection V09 series function Transmitter Built in Duplexer, PowerAmp and Band Pass CDMA Single Type T021 series Module * (CELL band) Filter (824MHz to 849MHz) Size (mm) Part number Correspondence system SAW D6CZ series US-PCS/W-CDMA II 5.0×5.0 Duplexer * 3.8 imes 3.8D5CF series CDMA/W-CDMA V 3.0×2.5 D5GA series CDMA/W-CDMA V D5GC series J-CDMA (27MHz) D5GG series J-CDMA (6MHz) D6GZ series US-PCS/W-CDMA II 2.5 imes 2.0D5JB series CDMA/W-CDMA V

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VCO

Part number	Functions	Application	Frequency (MHz)	Power supply voltage (V)	Package Typ. (mm)
VC-90 series		CDMA, GSM, PCS, PHS	700 to 2500	2.5 to 3.3	$5.0\times4.0\times1.55$
V10x series	Voltege Controlled	CDIVIA, GSIVI, FCS, FTIS	700 10 2300	2.5 10 5.5	$4.5\times3.2\times1.5$
V08 series	Oscillator		800 to 2500	2.8	$5.5\times4.8\times1.8$
V09 series		CDMA, PCS, GSM	800 10 2500	2.0	$5.0\times4.0\times1.4$

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Transmitter Module

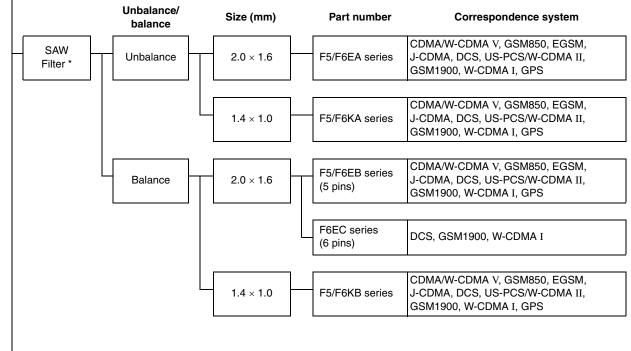
Part number	Functions	Application	Frequency (MHz)	Power supply voltage (V)	Package Typ. (mm)
T021 series	Built in Duplexer, PowerAmp and Band Pass Filter	CDMA (CELL band)	824 to 849	3.4	$8.0\times5.0\times1.4$

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SAW Duplexer for Mobile Communication System

Correspondence system	Size (mm)	Part Number	Remarks		
	3.8 imes 3.8	FAR-D5CF-881M50-D1F1	Two types of package are available		
CDMA/W-CDMA V	3.0 imes 2.5	FAR-D5GA-881M50-D1AA	Two types of package are available		
	2.5 imes 2.0	FAR-D5JB-881 M50-D3AA	Two types of package are available		
J-CDMA (27MHz)	3.0 imes 2.5	FAR-D5GC-911M50-D1CA	-		
J-CDMA (6MHz)	3.0 imes 2.5	FAR-D5GG-872M00-D1GA	-		
US-PCS/W-CDMA II	5.0 imes 5.0	FAR-D6CZ-1G9600-D1XC	Two types of package are available		
	3.0 imes 2.5	FAR-D6GZ-1G9600-D1ZA	Two types of package are available		
(Product of FUJITSU MEDIA DEVICES LIMITED					

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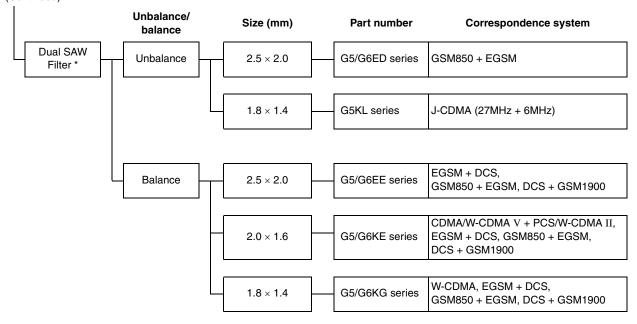
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SAW Filter for Mobile Communication System

Correspondence system	Transmission/ Reception	Size (mm)	Part number	Remarks
		2.0 × 1.6	FAR-F5EA-836M50-D27A	Unbalanced
	Transmission		FAR-F5KA-836M50-D4DF	Unbalanced
		1.4 × 1.0	FAR-F5KB-836M50-B4EG	Balanced 200 ohm output
			FAR-F5EA-881M50-D27B	Unbalanced
CDMA/W-CDMA V,		2.0 × 1.6	FAR-F5EB-881M50-B2JJ	5 pins, Balanced 100 ohm output
GSM850			FAR-F5EB-881M50-B28W	5 pins, Balanced 150 ohm output
	Reception		FAR-F5KA-881M50-D4CH	Unbalanced
			FAR-F5KB-881M50-B4ED	Balanced 100 ohm output
		1.4 × 1.0	FAR-F5KB-881M50-B4EA	Balanced 150 ohm output
			FAR-F5KB-881M50-B4EM	Balanced 150 ohm output
		2.0 × 1.6	FAR-F5EA-897M50-D27C	Unbalanced
	Transmission	1.4 × 1.0	FAR-F5KA-897M50-D4DC	Unbalanced
			FAR-F5EA-942M50-D27F	Unbalanced
EGSM		2.0 × 1.6	FAR-F5EB-942M50-B28E	5 pins, Balanced 150 ohm output
	Reception		FAR-F5KA-942M50-D4CJA	Unbalanced
		1.4 × 1.0	FAR-F5KB-942M50-B4EB	Balanced 150 ohm output
J-CDMA (32MHz)	Reception	1.4 × 1.0	FAR-F5KB-859M00-B4EE	Balanced 100 ohm output
			FAR-F6EA-1G5754-L2AZ	Unbalanced
		2.0 × 1.6	FAR-F6EB-1G5754-B2BS	5 pins, Balanced 100 ohm output
	-	1.4 × 1.0	FAR-F6KA-1G5754-L4AA	Unbalanced
GPS			FAR-F6KA-1G5754-L4AJ	Uubalanced
			FAR-F6KB-1G5754-B4GE	Balanced 100 ohm output, Low loss
			FAR-F6KB-1G5754-B4GU	Balanced 100 ohm output, High Attenuation
			FAR-F6EA-1G8425-D2ABA	Unbalanced
		2.0 × 1.6	FAR-F6EB-1G8425-B2BG	5 pins, Balanced 150 ohm output
DCS	Reception	2.0 × 1.0	FAR-F6EC-1G8425-B2CE	6 pins, Balanced 150 ohm output
	riccoption		FAR-F6KA-1G8425-D4CK	Unbalanced
		1.4 × 1.0	FAR-F6KB-1G8425-B4GA	Balanced 150 ohm output
		2.0 × 1.6	FAR-F6EA-1G8800-L2AN	For Full Band
	Transmission	1.4 × 1.0	FAR-F6KA-1G8800-L4AF	For Full Band
		1.4 ^ 1.0	FAR-F6EA-1G9600-D2AC	Unbalanced
			FAR-F6EB-1G9600-B2BK	5 pins, Balanced 100 ohm output
US-PCS/W-CDMA II,		2.0 × 1.6	FAR-F6EB-1G9600-B2BW	5 pins, Balanced 150 ohm output
GSM1900	Reception		FAR-F6EC-1G9600-B2CW	6 pins, Balanced 150 ohm output
	Reception		FAR-F6KA-1G9600-D4CR	Unbalanced
		14,10	FAR-F6KB-1G9600-B4GP	Balanced 100 ohm output
		1.4 × 1.0		•
		0.01.0	FAR-F6KB-1G9600-B4GB	Balanced 150 ohm output
		2.0 × 1.6	FAR-F6EA-1G9500-D2AL	Unbalanced
	Transmission	1 4 1 0	FAR-F6KA-1G9500-D4CD	Unbalanced
		1.4 × 1.0	FAR-F6KA-1G9500-D4DG	Unbalanced
			FAR-F6KB-1G9500-B4GJ	Balanced 100 ohm input
W-CDMA I		2.0 × 1.6	FAR-F6EB-2G1400-B2BN	5 pins, Balanced 100 ohm output
			FAR-F6EC-2G1400-B2CP	6 pins, Balanced 200 ohm output
	Reception		FAR-F6KA-2G1400-D4CG	Unbalanced
		1.4 × 1.0	FAR-F6KB-2G1400-B4GC	Balanced 100 ohm output
			FAR-F6KB-2G1400-B4GD	Balanced 200 ohm output Product of FUJITSU MEDIA DEVICES LIMITED

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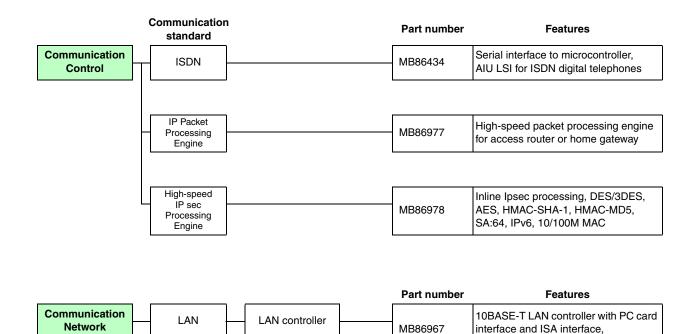
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SAW Dual Filter for Mobile Communication System

Correspondence system	Transmission/ Reception	Size (mm)	Part number	Remarks
		2.5 × 2.0	FAR-G6EE-1G8425-Y2PN	Balanced 150 ohm output, Opposite type of Filter position is available.
EGSM + DCS	Reception	2.0 × 1.6	FAR-G6KE-1G8425-Y4QG	Balanced 150 ohm output, Opposite type of Filter position is available.
		1.8 × 1.4	FAR-G6KG-1G8425-Y4SA	Balanced 150 ohm output, Opposite type of Filter position is available.
	Transmission	2.5 imes 2.0	FAR-G5ED-897M50-D2DE	Unbalanced
		2.5 × 2.0	FAR-G5EE-942M50-Y2PB	Balanced 150 ohm output, Opposite type of Filter position is available.
GSM850 + EGSM	Reception	2.0 × 1.6	FAR-G5KE-942M50-Y4QA	Balanced 150 ohm output, Opposite type of Filter position is available.
		1.8 × 1.4	FAR-G5KG-942M50-Y4SD	Balanced 150 ohm output, Opposite type of Filter position is available.
		2.5 × 2.0	FAR-G6EE-1G9600-Y2PR	Balanced 150 ohm output, Opposite type of Filter position is available.
DCS + GSM1900	Reception	2.0 × 1.6	FAR-G6KE-1G9600-Y4QB	Balanced 150 ohm output, Opposite type of Filter position is available.
		1.8 × 1.4	FAR-G6KG-1G9600-Y4SC	Balanced 150 ohm output, Opposite type of Filter position is available.
CDMA/W-CDMA V + US-PCS/W-CDMA II	Reception	2.0 × 1.6	FAR-G6KE-1G9600-Y4LY	Balanced 100 ohm output
J-CDMA (27 MHz + 6 MHz)	Transmission	1.8 × 1.4	FAR-G5KL-911M50-D4XA	Unbalanced, 1input/2output
W-CDMA I + V	Transmission	1.8 × 1.4	FAR-G6KG-1G9500-Y4PG	Balanced 200 ohm input
	Reception	1.8 × 1.4	FAR-G6KG-2G1400-Y4SH	Balanced 200 ohm output

(Product of FUJITSU MEDIA DEVICES LIMITED)

Communication Control/Communication Network



General purpose bus interface

Communication Control

ISDN

Part number	Functions	Communication standard	Power supply voltage (V)	Package QFP
MB86434	AIU LSI for ISDN digital telephones, Internal CODEC, DTMF tones, service tone, and ringer tone	-	$+5 \pm 5\%$	64P

Package: P - Plastic

IP Packet Processing Engine

Part number	Functions	Power supply voltage (V)	Package LQFP
MB86977	Enable to process following functions with hardware. IP Packet Forwarding Packet Filtering NAT PPPoE and more. Supports QoS, DMZ, IPv6 and more. 10/100M MAC (Conforms to IEEE802.3)	$\begin{array}{c} 3.3\pm0.3\\ 1.8\pm0.15\end{array}$	208P

Package: P - Plastic

High Speed IP sec Processing Engine

Part number	Functions	Power supply voltage (V)	Package FBGA
MB86978	Inline Ipsec processing, DES / 3DES,AES,HMAC - SHA-1,HMAC- MD5,SA:64,IPv6,10 / 100M MAC	$\begin{array}{c} 3.3 \pm 0.3 \\ 1.8 \pm 0.15 \end{array}$	337P 288P

Package: P - Plastic

Communication Network

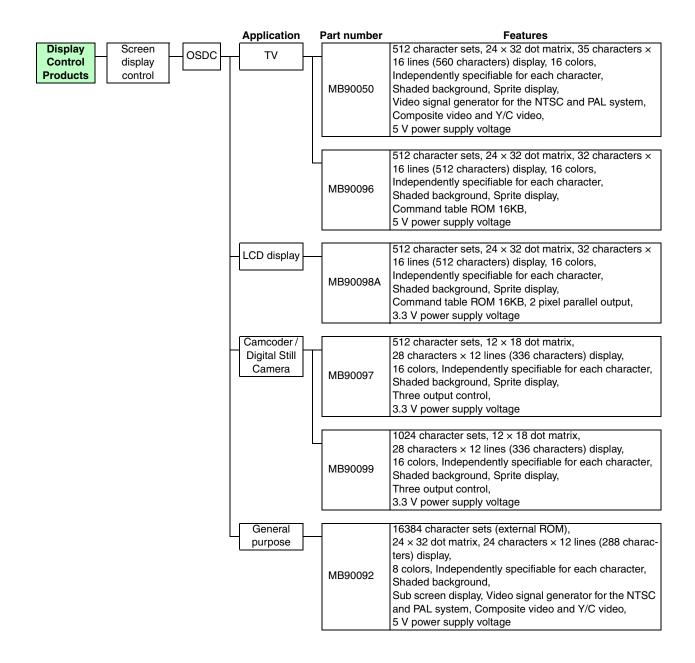
LAN

Part number	Functions	Communication standard	Power supply voltage (V)	Package LQFP
MR86967	10BASE-T Ethernet controller with PC card interface, ISA bus interface and General purpose bus interface	Conforms to IEEE 802.3	+5 ± 5%	100P

Note: Ethernet is a registered trademark of XEROX Corporation of the USA.

Package: P - Plastic

Display Control Products



Display Control Products

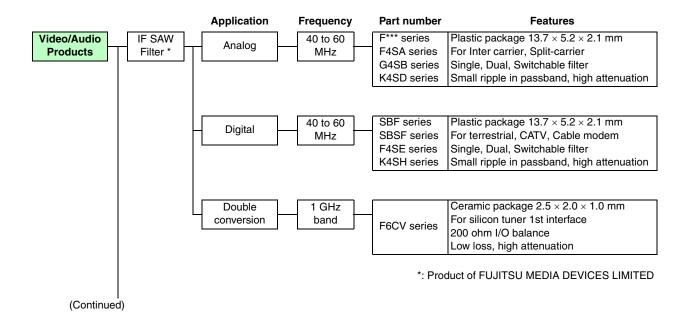
Screen Display Control

OSDC (On-Screen Display Controller)

			Number	Character		RGB	Analog	Sync	Power		I	Packa	age						
Part nur	mber	Character generator	of character set	dot	Screen	digital output	(video) output		supply voltage (V)	SH- DIP	SOP	QFP	SSOP	FLGA					
MB900)50	Internal ROM			35 characters × 16 lines	6bit (16 color selection in 64 colors)	Composite Video and Y/C video	NTSC PAL	+5 ±10%	_	_	48P	_	_					
MB900)96		512	24 × 32	32 characters				+5 ±10%	28P	28P			_					
MB900)98A	Internal ROM			× 16 lines	4bit (16 colors) ^{Unavailable}	4bit	4bit	I Inavailable I Inav	Linavailable	Unavailable Unavailab	I Inavailable I Inav	Linavailable	+3.3		28P			_
MB900)97		1024	28 12 × 18 character	28 characters			±0.3		_		20P	_						
MB900)99			12 × 10	× 12 lines									+2.4 to +3.6	_	_	_	20P	20P
MB900)92	External ROM	16384 (Max.)	24 × 32	24 characters × 12 lines	3bit (8 colors)	Composite Video and Y/C video	NTSC PAL	+5 ±10%		_	80P	_	_					

Package: P - Plastic

Video/Audio Products



Video/Audio Products

IF SAW Filter for Analog

IF SAW Filter for /	Analog	(Product of FUJITSU MEDIA DEVICES LIMITED)		
Applicable types	System	Video/Audio	Picuture carrier frequency (MHz)	Part number
	Inter-Carrier (single)	Video	58.75	F081EPL
	Split-Carrier (single)	Video	58.75	FAR-F4SA-58M750-A008
NTSC N	Split-Carrier (single)	Video	58.75	FAR-F4SA-58M750-A019
	Split-Carrier (single)	Audio	58.75	FAR-F4SA-54M250-B011
	Split-Carrier (dual)	Video/Audio	58.75	FAR-G4SB-58M750-D018
	Inter-Carrier (single)	Video	45.75	F072TPL-A
NTSC M/N	Split-Carrier (single)	Video	45.75	FAR-F4SA-45M750-A024
	Split-Carrier (single)	Audio	45.75	FAR-F4SA-41M250-B021
	Split-Carrier (dual)	Video/Audio	45.75	FAR-G4SB-45M750-D025
	Inter-Carrier (single)	Video	38.90	FAR-F4SA-38M900-A041
	Split-Carrier (single)	Video	38.90	FAR-F4SA-38M900-A071
PAL B/G/D/K/I	Split-Carrier (single)	Video	38.90	FAR-F4SA-38M900-A072
	Split-Carrier (single)	Audio	38.00	F337MPL
	Split-Carrier (single)	Audio	38.90	FAR-F4SA-40M400-B071
	Split-Carrier (Switchable)	Video + Video	38.00	FAR-K4SD-38M000-F002
PAL B/G, D/K, NTSC M/N	Split-Carrier (Switchable)	Video + Video	38.00	FAR-K4SD-38M000-F011
	Split-Carrier (Switchable)	Video + Video	38.90	FAR-K4SD-38M900-F003
	Split-Carrier (Switchable)	Audio + Audio	33.90/38.90	FAR-K4SD-40M400-G001
PAL D/K/I, B/G, L/Ľ	Split-Carrier (Switchable)	Audio + Audio	33.90/38.90	FAR-K4SD-40M400-G002
1 AL D/11/1, D/G, L/L	Split-Carrier (Switchable)	Audio + Audio	33.90/38.90	FAR-K4SD-40M400-G031
	Split-Carrier (dual)	Audio + Audio	33.90/38.90	F817JPL

IF SAW Filter for Digital

(Product of FUJITSU MEDIA DEVICES LIMITED)

Applicable types	Center frequency (MHz)	3 dB Bandwidth (MHz)	Part number
DAB	38.912	1.50	SBF0402GPL
	44.000	1.70	SBF0402JPL
OOB	44.000	1.70	FAR-F4SE-44M000-A011
UОВ	44.000	2.60	FAR-F4SE-44M000-H0A6
	44.000	4.00	FAR-F4SE-44M000-H0A3
	36.000	8.10	FAR-F4SE-36M000-A005
	36.125	6.10	FAR-F4SE-36M125-A001
	36.125	7.00	SBF0407BPL
	36.125	8.10	SBF0408KPL
	43.750	6.00	FAR-F4SE-43M750-A006
	43.750	6.00	FAR-F4SE-43M750-H0AB
	44.000	5.35	FAR-F4SE-44M000-H0AG
	44.000	5.37	FAR-F4SE-44M000-H0A4
	44.000	5.42	FAR-F4SE-44M000-H0A8
CATV/TV	44.000	5.49	FAR-F4SE-44M000-H0A1
(US/Euro)	44.000	5.50	FAR-F4SE-44M000-H0AH
	44.000	6.00	FAR-F4SE-44M000-H0A9
	44.000	6.12	FAR-F4SE-44M000-H0A2
	44.000	6.20	FAR-F4SE-44M000-H0AA
	44.000	8.00	SBF0408LPL
	47.250	6.20	FAR-F4SE-47M250-H0AC
	36.000	6.4/7.4 (Switchable)	FAR-K4SH-36M000-L0E1
	36.000	7.0/7.9 (Switchable)	SBSF03ABPL
	36.125	6.0/7.9 (Switchable)	FAR-K4SH-36M125-F001
	36.125	7.0/7.9 (Switchable)	SBSF03AAPL
	57.000	5.30	FAR-F4SE-57M000-H0JC
CATV/TV	57.000	5.40	FAR-F4SE-57M000-H0J9
(Japan)	57.000	5.62	FAR-F4SE-57M000-H0J6
	57.000	5.62	FAR-F4SE-57M000-H0J3
	35.230	8.00	FAR-F4SE-35M230-A013
TV tuner	36.125	6.90	FAR-F4SE-36M125-H0E8
	36.125	7.60	FAR-F4SE-36M125-H0E5
TV/STB	36.125	7.90	FAR-F4SE-36M125-H0E7

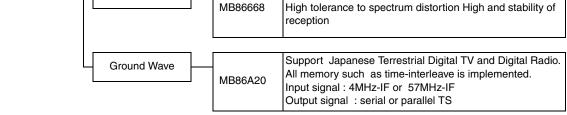
IF SAW Filter for Double ConversionI

(Product of FUJITSU MEDIA DEVICES LIMITED)

Applicable types	Center frequency (MHz)	Bandwidth (MHz)	Part number		
1st IF	1220.000	8.00	FAR-F6CV-1G2200-C27A		

Video/Audio Products/Demodulator Products

Application Capacity Organization Part number Features EDID DTV/display 2K-bit 256 × 8 MB85RF402 For 4 DDC(I²C) ports memory for HDMI Application Part number Features Digital Small 48 pin package Satellite Demodulator High tolerance to spectrum distortion High and stability of MB86667 reception Blind Scan support Cable Small 48 pin package



(Continued)

EDID memory

OMB85RF402 FRAM 256 × 8 For 4 DDC(l ² C) ports 3.8 to 5.5 16P	Part Number	Memory	Organization (W × b)	Interface	Supply Voltage (V)	Packages TSSOP
	OMB85RF402	FRAM	256 × 8	For 4 DDC(I ² C) ports	3.8 to 5.5	16P

 \bigcirc : New released.

Pakage : P - Plastic

Demodulator Products

Satellite

Part number	Function	Power supply voltage (V)	Package
Faithumber	T unction	Power supply voltage (v)	QFP
MB86667	QPSK demodulator DVB-S and DSS support	1.65 to 1.95 3.0 to 3.6	48P

Package: P - Plastic

Cable

Part number	Function	Power supply voltage (V)	Package
Farthumber		Power supply voltage (v)	QFP
MB86668	QAM demodulator DVB-C support	1.65 to 1.95 3.0 to 3.6	48P

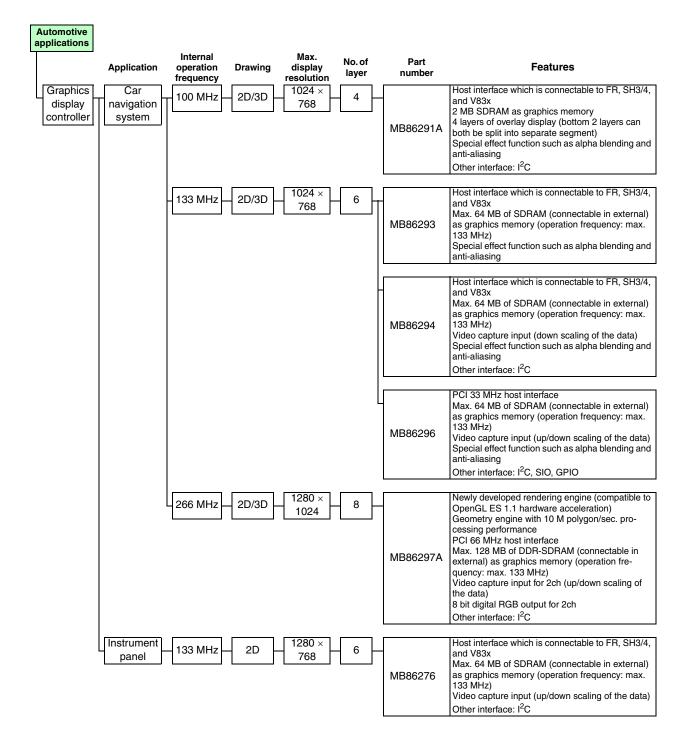
Package: P - Plastic

Ground Wave

Part number	Function	Power supply voltage (V)	Package FBGA
MB86A20	13 segment OFDM demodulator ISDB-T support	1.4 to 1.6 1.65 to 1.95 3.0 to 3.6	144P

Package: P - Plastic

Automotive Applications

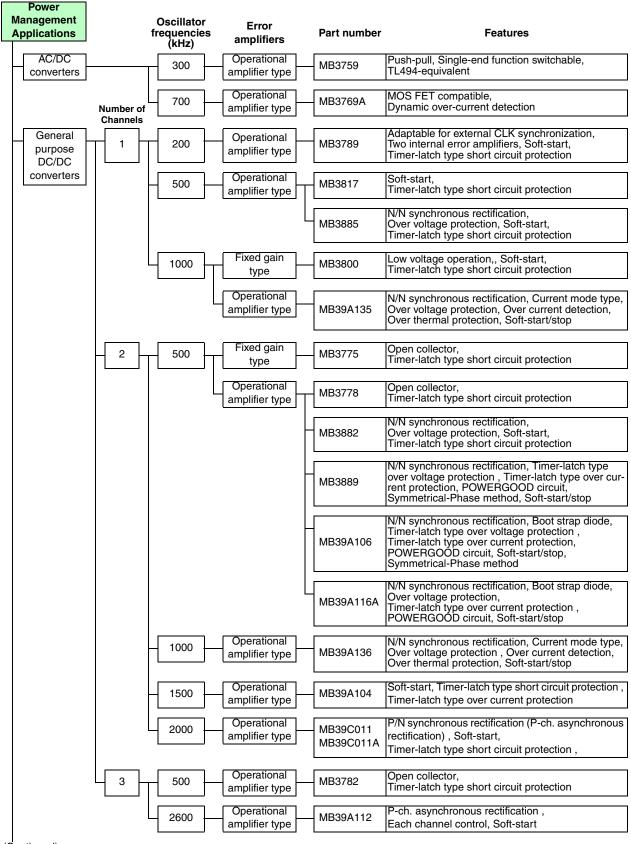


Automotive Applications

Graphics Display Controller

Part number	Internal operation frequency	Rendering engine	Geometry engine	Max. graphics memory	Drawing	Display resolution (pixel)	No. of layer	Texture mapping (pixel)	Video capture input	Video scaling	Video output	Host interface	supply		Package
MB86291A	100 MHz			2 MB SDRAM (built-in)			4	Max. 256 × 256	YUV	-	RGB analog/ digital		I/O: 3.3 V Internal: 2.5 V	-30 to +85	QFP- 208P
MB86293					_	Max. 1024 × 768			-	-	RGB digital	32 bit parallel			QFP- 256P
MB86294	133 MHz 266 MHz 133 MHz	Built-in	Built-in	64 MB SDRAM (external)			8 6 (included 1 alpha plane)		YUV	Down	RGB analog/ digital		I/O: 3.3 V Internal: 1.8 V		QFP- 256P BGA- 256P
MB86296								Max. 4096	YUV/ RGB	Up/ Down	uigitai	PCI 33 MHz			BGA- 256P
MB86297A		266 MHz		128 MB DDR- SDRAM (external)		Max. 1280 × 1024 8 (plus 4 alpha plane)	× 4096	YUV × 2/ RGB + YUV	Up/ Down	RGB digital × 2	PCI 66 MHz	I/O: 3.3 V Internal: 1.2 V	-40 to +85	TEBGA- 543P	
MB86276			-	64 MB SDRAM (external)	2D	Max. 1280 × 768	6 (included 1 alpha plane)		YUV/ RGB	Up/ Down	RGB digital	32/16 bit parallel Address/ data bus multiplex	I/O: 3.3 V Internal: 1.8 V		PBGA- 320P

Packages: P - Plastic



(Continued)

AC/DC Converters

		Power supply	No. of	Operating oscillator	Refere	nce voltage	Package
Part number	Function	voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	SOP
MB3759	PWM-type controllers for AC/DC converters	+7 to +32	1	300	5	5.0	16P
MB3769A		+12 to +18		700	5	2.0	16P

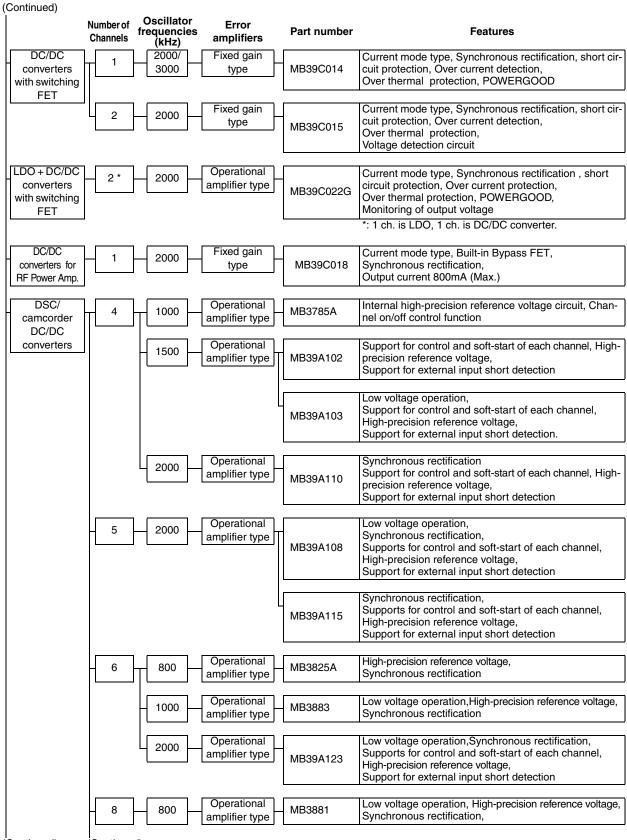
Packages: P - Plastic

General Purpose DC/DC Converters

Part number	Function	Power supply		Operating oscillator frequency	Referen	ice voltage	Solutions	Package		
		voltage (V)	channels	(kHz) (Max.)	(V) (Typ.)	Precision (%)		SOP	SSOP	TSSOP
MB3789		+3.0 to +18		200	2.5	4.0	Up conversion	-	16P	-
MB3817	PWM-type controllers for DC/	+2.5 to +18	1	500	1.5	2.0	Up conversion Down conversion Invert	I	16P	_
MB3885	DC converters	+5.5 to +18	1		1.25	1.0	Down conversion	-	20P	-
MB3800		+1.8 to +15		1000	0.5	4.0	Up conversion	8P	8P	-
OMB39A135		+4.5 to +25		1000	0.7	1.0	Down conversion	-	-	24P
MB3775		+3.6 to +18			1.28	1.5	Up conversion	16P	16P	-
MB3778		+3.6 10 +18	2		2.46	2.0	Down conversion Invert	16P	16P	
MB3882		E E to 10		500	1.25			-	24P	
MB3889		+5.5 to +18			1.23			_	-	30P
MB39A106	PWM-type controllers for DC/	+6.5 to +18						-	-	30P
MB39A116A	DC converters	+0.5 10 +18			1.00	1.0	Down conversion	-	-	30P
OMB39A136		+4.5 to +25		1000	0.7			_	-	16P
MB39A104		+7 to +19		1500	1.24			-	24P	-
MB39C011 MB39C011A	-	+4.5 to +17		2000	1.0			_	-	16P
MB3782	PWM-type controllers for DC/	+3.6 to +18	3	500	2.5	2.0	Up conversion Down conversion Invert	20P	-	_
MB39A112		+7 to +25		2600	(1.0/ 1.23)	1.0	Down conversion	Ì	_	20P

○: New product

Packages: P - Plastic



(Continued) (Continued)

DC/DC converters with switching FET

Part number	Function	Power	No. of	Operating oscillator	Referen	ice voltage	Output current	Switchi ON res	istance	Solutions	Pack	age	
Fart number	Function	supply voltage (V)	channels	frequency (kHz) (V) (Max.) (Typ.)	Precision (%)	DC/DC (mA) (Max)		Nch MOS		QFN	SON		
	PWM type DC/DC converters		+2.5 to +5.5	1	2000/3200 (Fix)	1.20	2.0	800	0.3	0.2	Down	-	10P
			2	2000 (Fix)	1.30	2.0	000	0.5	0.2	conversion	24P	_	

Packages: P - Plastic

DC/DC converters with switching FET + LDO

	Part number	Function	Power supply	No. of	Operating oscillator	Reference voltage		Precision	Output current		•	I/O potential	Solutions	Package
	Fart number	Function	voltage (V)	channels	frequency (kHz)	(V) (Typ.)	(V) (Typ.)	(%)		Pch MOS (Ω) (Typ)			Solutions	SON
		DC/DC converter	+2.5 to +5.5	1	2000 (Fix)	0.3	-	±2.5	600	0.3	0.2	-	Down	
	©MB39C022G	LDO		1	I	-	3.3 (Fix)	±2.5	300	-	I	200	conversion	10P
©: Now planning Packages: P - Plastic											- Plastic			

DC/DC converters for RF Power Amp.

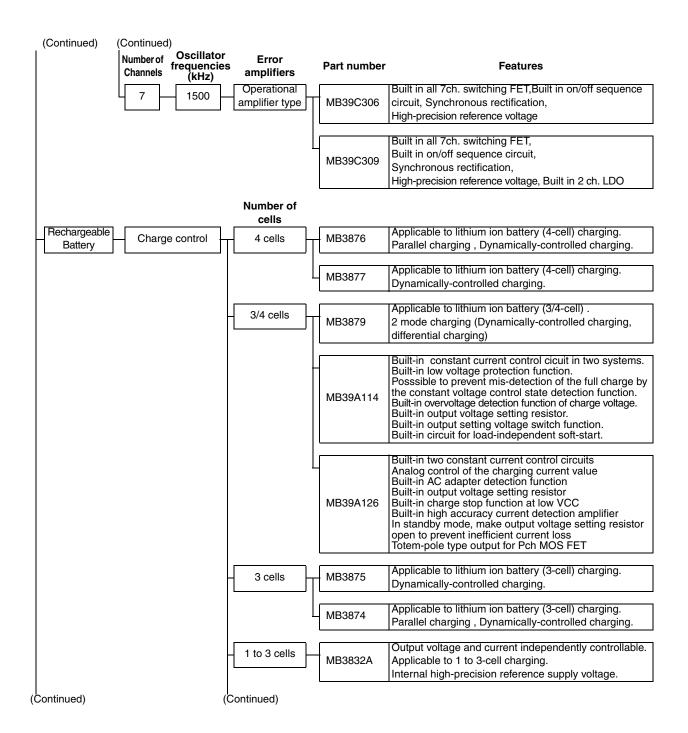
Part number	Function	Power supply	No. of	Operating oscillator	oscillator voltag		Output current			/itching F N resistar		Solutions	Package
			channels	(KHZ)	(V) (Typ.)	on	DC/DC (mA) (Max)	Bypass FET (mA) (Max)	(0)	Nch MOS (Ω) (Typ)	Bypass FET (Ω) (Typ)	Solutions	QFN
MB39C018	PWM type DC/DC converters Built in Bypass FET	+2.5 to +5.5	1	2000 (Fix)	1.24	1.5	800	1000	0.3	0.2	0.08	Down conversion	24P

Packages: P - Plastic

DSC/Camcorder DC/DC Converters

Part number	Function supply No. of oscillator voltage			Solutions	Drive	Package					
i art number	1 unction	voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	Controlls	circuit	LQFP	BCC	TSSOP
MB3785A		+4.5 to +18		1000	2.5		Down conversion	PNP :4	48P		
MB39A102		+2.5 to +11		1500				Pch : 3, Nch : 1	-	32P	30P
MB39A103		+1.7 to +11	4	1500			Up conversion Down conversion Up/Down conversion	Pch : 1, Nch : 3	—	32P	30P
MB39A110	PWM-type	+2.5 to +11			2.0			Pch : 3, Nch : 1	—		38P
MB39A108		PWM-type controllers +1.7 to +11 5	2000				Pch : 3, Nch : 2	—	40P	38P	
MB39A115	for DC/DC	+1.7 to +11	5			1.0		Pch : 4, Nch : 1	—	40P	38P
MB3825A	conveniers	+2.5 to +12		800	1.5		Down conversion	PNP : 6	64P**	_	_
MB3883		+1.7 to +9	6	1000	2.5		Up conversion Down conversion Up/Down conversion	Pch : 2, Nch : 4	48P	48P	_
MB39A123		+1.7 to +11		2000	2.0		Up conversion Down conversion Up/Down conversion Invert	Pch : 4, Nch : 2	48P	48P	_
MB3881		+1.8 to +13	8	800	2.5		Down conversion Up/Down conversion	Pch : 7, Nch : 1	64P*		_

*: 0.4 mm pitch



DSC/Camcorder DC/DC Converters

Part number	Function	Power supply	No. of	Operating oscillator	-	erence Itage	Solutions	Drive circuit	Package
r art number	i unotion	voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)		Brive circuit	FBGA
	PWM-type DC/DC	+2.5 to +6		1500	2.4	1.0	Up conversion Down conversion	All channel with built-in switching	103P
	converters	+2.5 to +5.5	7 (DC/DC) 2 (LDO	1500 2.4 1.		1.0	Up/Down conversion Invert	FETs	82P

Packages: P - Plastic

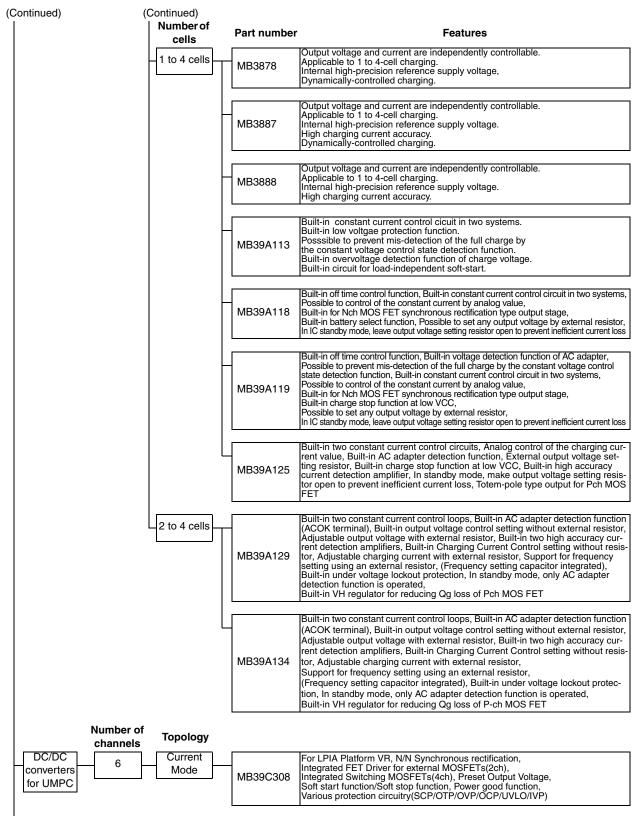
Rechargeable Battery (Charge control)

		Power					Operating		P	ackag	e
Part number	Function	supply	Output voltage	Pre	cision (%)	Number	oscillator frequency	Solutions			
		voltage (V)	(V)	Ta = +25 °C	Ta = -30 to +85 °C	of cells	(kHz) (Max.)		SSOP	LQFP	QFN
MB3876		+7 to +25	16.8	±0.8	±1.0	4			24P	-	-
MB3877		Ŧ7 10 Ŧ23	10.0	±0.0	±1.0	-			24P	-	-
MB3879			12.6/16.8	±0.8	±1.0			Down conversion		48P	
WIB6075		ol IC	12.3/16.4	±0.9	±1.1					101	
MB39A114	Charge control		+8 to +25	±0.5	±0.74 *	3/4	500		24P	-	-
MB39A126	DC/DC converters		12.0/10.0	±0.6	±0.80 *		500		24P	_	28P
MB3875		+7 to +25	12.6	±0.8	±1.0	2			24P	-	-
MB3874		+7 10 +25	12.0	⊥ 0. 0	±1.0	3			24P	-	_
MB3832A		+3.6 to +18	Any voltage level	±0.5	±1.0*	1 to 3			20P	-	-

* : Ta = -10 to +85 °C

Package: P-plastic

Power Management Applications



(Continued)

Rechargeable Battery (Charge control)

		Power	er		Operating				Package		е
Part number	Function	supply	Output	Pre	cision (%)	Number	oscillator frequency	Solutions			
		voltage (V)	voltage (V)	Ta = +25 °C	Ta = -30 to +85 °C	of cells	(kHz) (Max.)		SSOP	TSSOP	QFN
MB3878		+7 to +25	4.2 V/cell	±0.8	±1.0				24P	_	-
MB3887			4.2 7/061	+0.6 -0.4			500	Down conversion	24P	_	-
MB3888			Any voltage level		±0.74 *	1 to 4			20P	_	_
MB39A113	Charge		4.2 V/cell						24P	-	-
MB39A118	control DC/DC	ntrol			±0.74 *		1000		-	-	28P
MB39A119	converters	+8 to +25		±0.5					_	-	28P
MB39A125							500		24P	-	28P
MB39A129			4.145V/Cell, 3.75V/Cell, Any voltage level		±0.7 *	2 to 4	2000		24P	_	_
OMB39A134			4.2V/Cell, 4.1V/Cell, Any voltage level	4.2V/Cell, 4.1V/Cell, Any voltage	±0.7 *	2 to 4	2000		_	24P	_

○: New product

DC/DC converters for Ultra Mobile PC

		Input	Number	Number Oscillator		Out	out feature	\$		Package
Part number	Function	voltage (V)	of channels	frequencies (kHz)	Pin name	Preset Output Voltage (V)	FET	Drive or Output current (A) (Max)	Solutions	PBGA
	DC/DC				CH1	5	External	2		
				700	CH2	3.3	External	4.5	Down	
OMB39C308	converters for LPIA	+5.5 to	6		CH3	1.8/1.5		2.7		208P
	Platform	+12.6	0	(Fix)	CH4	0.9/0.75	Integrated	1.5	conversion	2069
	VR		-	CH5	1.5	Integrated	2.5			
					CH6	1.05		3.5		

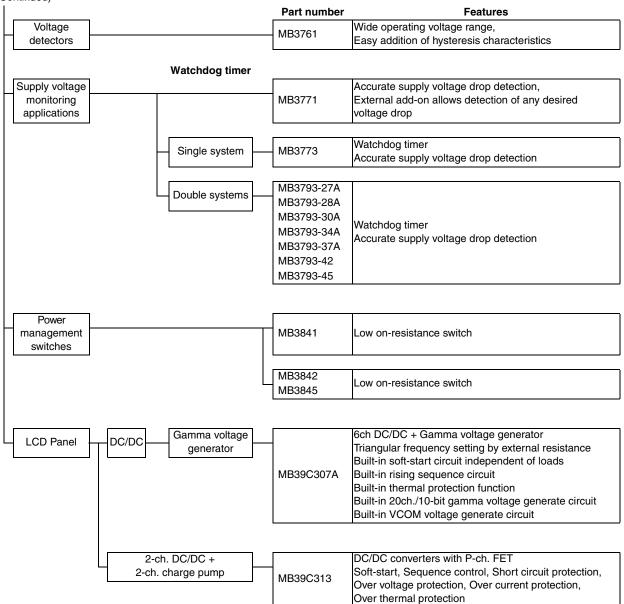
LPIA=Low Power Intel Architecture®

⊖: New product

Package: P-plastic

Power Management Applications

(Continued)



Voltage Detectors

Part number	Function	Power supply voltage	Reference voltage	Package
Part number	i unction	(V)	(V) (Typ.)	SOP
MB3761	Voltage detector	+2.5 to +40	1.2	8P

Package: P - Plastic

Supply Voltage Monitoring Applications

Dentaria	Franklan	Power supply	Data dia mandra (10)	Reset certified	Pac	kage
Part number	Function	voltage (V)	Detection voltage (V)	voltage (V) (Typ.)	PackSOP8P8P8P8P8P8P	SSOP
MB3771	Supply voltage monitoring applications	+3.5 to +18	Any voltage level in		8P	-
MB3773	Supply voltage monitoring applications with watchdog timer	+3.5 to +16	addition to 4.2 V		8P	-
MB3793-27A *1		+4 (Max.)	2.7±0.07		8P	8P
MB3793-28A *1		+4 (IVIAX.)	2.8±0.07		8P	8P
MB3793-30A ^{*1}			3.0±0.07	0.8	8P	8P
	Supply voltage monitoring applications with dual watchdog timer systems		3.4±0.08		8P	(8P) ^{*2}
MB3793-37A ^{*1}		+6 (Max.)	3.7±0.1		8P	(8P) ^{*2}
MB3793-42 *1			4.2±0.1		8P	(8P) ^{*2}
MB3793-45 ^{*1}			4.5±0.1		8P	8P

*1:Detection voltages of the MB3793 series are available in the range from 2.4 V to 4.9 V in 0.1 V increments. Package: P - Plastic Consult with supplier.

*2:() option

Switching Applications

Part number	Function	Power supply	Number of	On-resistance	Drive current	Package	
Faithumber	Tunction	voltage (V) (Max.)	channels	(Ω)	(A) (Max.)	SOP	SSOP
MB3841	Power management switch	5.5	1	0.045	2.0	8P	-
MB3842			2	0.1	0.6		20P
MB3845			2	0.1	0.0		201

Package: P - Plastic

LCD Panel

				DC/DC Block						Gamma volrtage generator block		
	Part number	Function	Power supply voltage (V)	Number of channels	Reference voltage (V)	Precision (%)	Oscillation frequency (kHz)(Max)	Solution	Gamma voltage number of channel	VCOM voltage number of channel	DAC (bit)	всс
	OMB39C307A	DC/DC + Gamma voltage generator	+4.5 to +17	6	1 1.25	± 1.0	600	Step down 3ch Step up 2ch Invert 1ch	20	1	10	92P *
(: New product									Pack	age: P	- Plastic

*: With exposed pad

LCD Panel

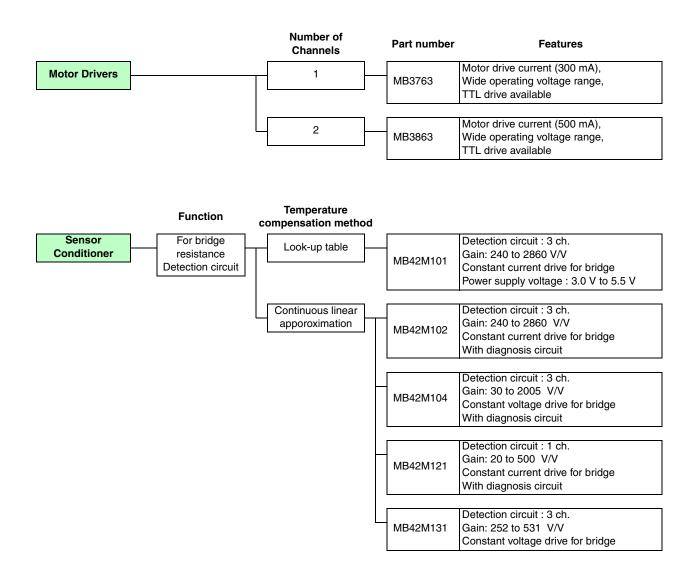
Part number	Function	Power supply voltage (V)	Number of channels	Reference voltage (V)	Precision	Oscillation frequency (kHz)	Solution	Package TSSOP
	2ch. DC/DC + 2ch.	+8 to +14	4	1.213	± 1.0%		Step down	
⊚MB39C313				1.146	± 1.0%	500/750	Step up	28P *
OMD390313	charge pump			0	± 36mV	500/750	Invert charge pump	
				1.213	± 1.0%		Step up charge pump	

©: Now planning

*: With exposed pad

Package: P - Plastic

Motor Drivers/Sensor Conditioner



Motor Drivers

Part number	Function	Number of Channels	Output current (mA)	Power supply voltage (V)	Package SOP
MB3763	Reversible motor drivers	1	300	+4 to +18	8P
MB3863		2	500	+4 to +36	20P

Package: P - Plastic

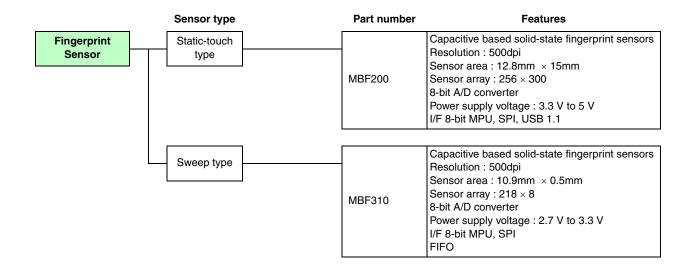
Sensor Conditioner

		Temperature	Numberof		Power		Pac	kage
Part number	Function	compensation method	detection circuits	Gain	supply voltage (V)	Others	всс	SSOP
MB42M101	For bridge resistance Detection circuit	Look-up table	3	240 to 2860 V/V	3.0 to 5.5	Digital compensation Constant current drive Built-in memory 1280 bits	32P	_
MB42M102	For bridge resistance Detection circuit	Continuous linear apporoximation	3	240 to 2860 V/V	4.5 to 5.5	Digital compensation Constant current drive Built-in memory 1280 bits Diagnosis circuit	40P	_
MB42M104	For bridge resistance Detection circuit	Continuous linear apporoximation	3	30 to 2005 V/V	4.5 to 5.5	Digital compensation Constant voltage drive Built-in memory 1280 bits Diagnosis circuit	40P	-
⊚MB42M121	For bridge resistance Detection circuit	Continuous linear apporoximation	1	20 to 500 V/V	2.7 to 3.6	Digital compensation Constant voltage drive Built-in memory 1280 bits Diagnosis circuit	_	20P
⊚MB42M131	For bridge resistance Detection circuit	Continuous linear apporoximation	3	252 to 531 V/V	2.7 to 3.6	Digital compensation Constant voltage drive	20P	_

⊚: Now planning

Package: P - Plastic

Fingerprint Sensor



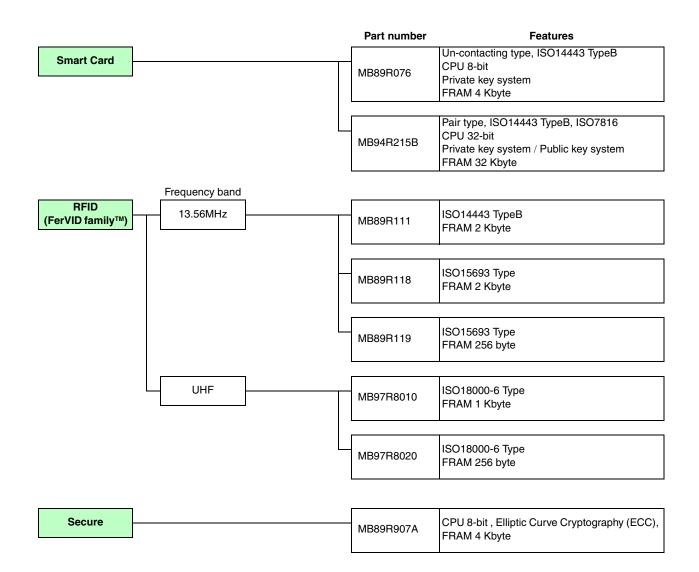
AUGE

Fingerprint Sensor

Part number		Sensor area	Sensor array	Power supply voltage	Interface	Others	Pacl	kage
Fait number	(dpi)	(mm)	(pixel)	(V)	Interface	Others	TSOP	FBGA
MBF200	500	12.8 × 15.0	256 × 300	3.3 to 5.0	8bit MPU SPI USB 1.1	-	80P	-
MBF310		10.9 × 0.5	218 × 8	2.7 to 3.3	8bit MPU SPI	FIFO	-	43P

Package: P - Plastic

Smart Card/RFID (FerVID family™) /Secure



Smart Card/RFID (FerVID family™) /Secure

Smart Card

Part number	Interface	CPU (bit)	FRAM (byte)	ROM (byte)	SRAM (byte)	Code Type	Shipment form
MB89R076	ISO14443 TypeB	8	4K	32K	512	DES	An exclusive package
MB94R215B	ISO14443 TypeB, ISO7816	32	32K	128K	8K	DES/RSA	An exclusive package

RFID (FerVID family™)

Part number	Frequency band	Interface	Transmission speed (Reader/Writer -> LSI)	Transmission speed (LSI -> Reader/Writer)	FRAM (byte)	Shipment form
MB89R111	ISO14443 TypeB		106kbps, 212kbps	106kbps, 212kbps	2K	Wafer
MB89R118	13.56MHz	ISO15693	26.48kbps (52.97kbps)	26.48kbps (52.97kbps)	2K	Wafer (With a golden Bump)
MB89R119		ISO15693	26.48kbps (52.97kbps)	26.48kbps (52.97kbps)	256	Wafer (With a golden Bump)
OMB97R8010	UHF	ISO18000-6 TypeB	10kbps, 40kbps	10kbps, 40kbps	1K	Wafer (With a golden Bump)
OMB97R8020	On	ISO18000-6 TypeB	10kbps, 40kbps	10kbps, 40kbps	256	Wafer (With a golden Bump)

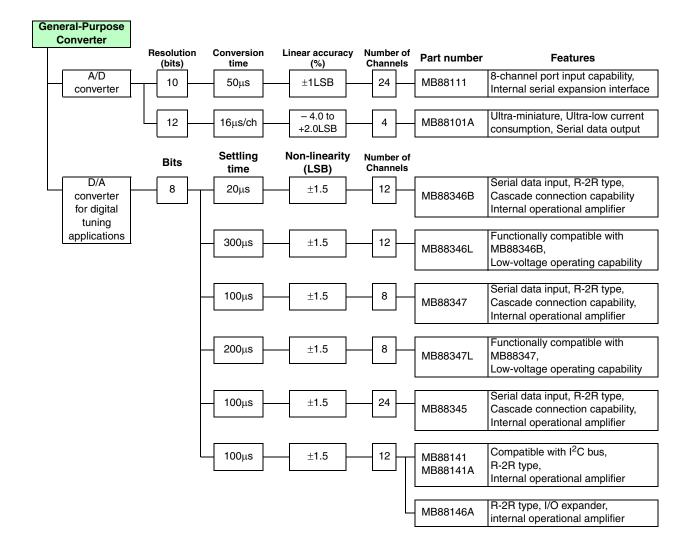
 \bigcirc : New product

Secure

-	Part number	CPU	FRAM	ROM	SRAM	Code Type	Power supply voltage	Package
	i ult humber	(bit) (byte)	(byte)	(byte)		(V)	QFP	
	MB89R907A	8	4K	32K	1K	Elliptic Curve Cryptography (ECC)	$+5\pm5\%$	48P

Package: P - Plastic

General-Purpose Converter



General-Purpose Converter

A/D Converter

Part	t number	Function	Conversion	Conversion time	Linearity error (%)	Power supply	Package					
			method	(μs/ch) (Max.)	(Max.)	voltage (V)	DIP	SOP	SSOP	QFP	SH-DIP	
ME	B88111	24-ch 10-bit A/D converter	Successive approximation	50	±1 LSB	+3.5 to +5.5	_	-	_	44P	48P	
ME	B88101A	4-ch 12-bit A/D converter		16 (at 5 V±10%)	-4.0 to +2.0 LSB	+3.3 to +5.5	16P	16P	16P	_	_	

Packages: P - Plastic

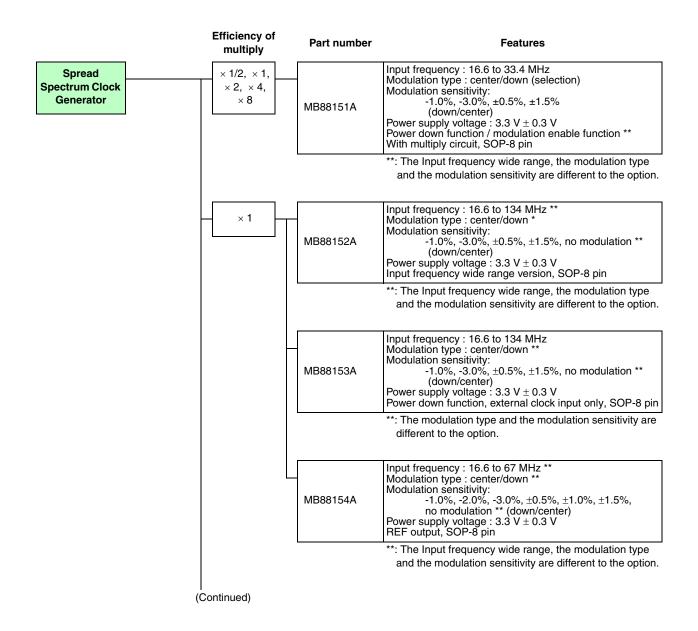
D/A Converter for Digital Tuning Applications

Part number	Function	Settling time	Power consumption	Non- linearity	Power supply voltage		Pac	kage	
T art number	T unction	(μs) (Max.)	(mW) (Typ.)	error (LSB)	(V)	DIP	SOP	SSOP	QFP
MB88346B	12-ch 8-bit D/A converter (internal operational amplifier)	20	14		+5±10%	20P	20P	20P	-
MB88346L	12-ch 8-bit D/A converter (internal operational amplifier, low voltage operation)	300	5		+2.7 to +3.6	20P	20P	20P	_
MB88347	8-ch 8-bit D/A converter (internal operational amplifier)	100	9		+5±10%	16P	16P	16P	_
MB88347L	8-ch 8-bit D/A converter (internal operational amplifier, low voltage operation)	200	4.2	±1.5	+2.7 to +3.6	16P	16P	16P	_
MB88345	24-ch 8-bit D/A converter (internal operational amplifier)	100	27					_	32P
MB88141 *	12-ch 8-bit D/A converter (compatible with I ² C bus,		15		+5±10%	24P	24P	24P	_
MB88141A *	\mathbf{C}			2		2	_		
MB88146A	12-ch 8-bit D/A converter (I/O expander, internal operational amplifier)		14.5		Digital:+2.7 to +5.5 Analog:+5±10%	24P	-	24P	-

Package: P - Plastic

* "Purchase of Fujitsu Microelectronics I²C components conveys a license under the Philips I²C Patent Rights to use these components in an I²C system, provided that the system conforms to the I²C Standard Specification as defined by Philips."

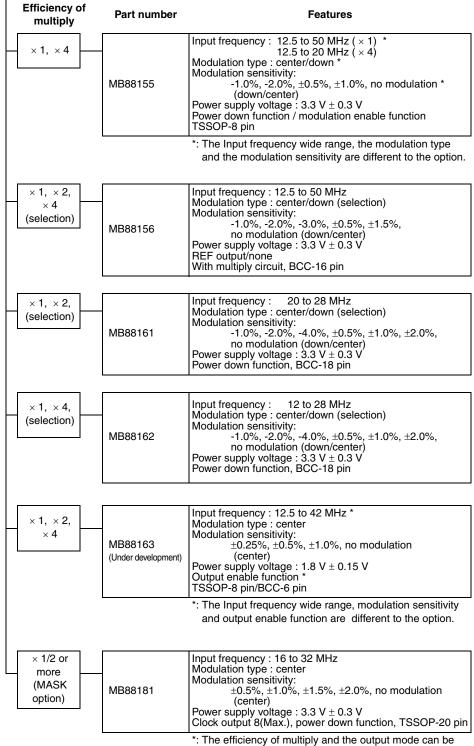
Spread Spectrum Clock Generator



Spread Spectrum Clock Generator

		Power	Input	Efficiency		Modulation	Modulation		Package
Part number	Function	supply voltage	frequency (MHz)	of multiply	frequency (MHz)	Туре	sensitivity	Other	SOP
MB88151A-100								PD function disable	
MB88151A-101				× 1	16.6 to 33.4			PD function enable	
MB88151A-200								PD function disable	-
MB88151A-201			10.0 to 00.4	× 2	33.2 to 66.8		-1.0%, -3.0% (down)	PD function enable	
MB88151A-400			16.6 to 33.4	× 4	66.4 to	Down or center	±0.5%, ±1.5% (center) no modulation	PD function disable	8P
MB88151A-401				× 4	133.6	(selection)	(no modulation setting is no PD	PD function enable	OF
MB88151A-500			8.3 to 16.7	× 1/2	8.3 to 16.7		product)	PD function disable	
MB88151A-501				× 1/2	8.5 10 10.7			PD function enable	-
MB88151A-800				× 8	66.4 to			PD function disable	-
MB88151A-801	EMI noise reduction	3.3		× 0	133.6			PD function enable	
MB88152A-100	PLL (SSCG)	± 0.3	16.6 to 40 33 to 67		16.6 to 40 33 to 67	Down	-1.0%, -3.0%		
MB88152A-110			33 to 67 40 to 80 66 to 134		40 to 80 66 to 134	Center	±0.5%, ±1.5%		
MB88152A-101			16.6 to 40	4	16.6 to 40	Down	-1.0%, -3.0% no modulation		0.0
MB88152A-111			33 to 67	× 1	33 to 67	Center	$\pm 0.5\%, \pm 1.5\%$ no modulation	-	8P
MB88152A-102			40 to 80		40 to 80	Down	-1.0%, -3.0% no modulation		
MB88152A-112			66 to 134		66 to 134	Center	$\pm 0.5\%$, $\pm 1.5\%$ no modulation		
MB88153A-100			16.6 to 40		16.6 to 40	Down	-1.0%, no modulation		
MB88153A-101			66 to 134	× 1	66 to 134	Down	-3.0%, no modulation	PD function	8P
MB88153A-110			33 to 67		33 to 67	Center	±0.5%, no modulation	enable	
MB88153A-111			40 to 80		40 to 80	00.1101	±1.5%, no modulation		
MB88154A-102			33 to 67		33 to 67	Down	-1.0%, -2.0%, 3.0%,		
MB88154A-103	16.6	16.6 to 40	× 1	16.6 to 40	Bowin	no modulation	REF output	8P	
MB88154A-112			33 to 67	57 × 1	33 to 67	7 Center	±0.5%, ±1.0%,	enable	
MB88154A-113			16.6 to 40		16.6 to 40	00.1101	±1.5%, no modulation		

Package: P - Plastic (Continued) (Continued)



arbitrarily set by the mask option.

(Continued)

		Power	Input	Efficiency	Output				Pack	age								
Part number	Function	supply voltage (V)	fraguanay	-	frequency (MHz)	Modulation Type	Modulation sensitivity	Other	TSSOP	BCC								
MB88155-100 MB88155-101			12.5 to 25 25 to 50		12.5 to 25 25 to 50		-1.0%, -2.0% no modulation	PD function disable										
MB88155-102 MB88155-103			12.5 to 25 25 to 50		12.5 to 25 25 to 50	Down	-1.0%, -2.0%	PD function enable										
MB88155-110 MB88155-111			12.5 to 25 25 to 50	× 1	12.5 to 25 25 to 50		±0.5%, ±1.0% no modulation	PD function disable										
MB88155-112 MB88155-113			12.5 to 25 25 to 50		12.5 to 25 25 to 50	Center	±0.5%, ±1.0%	PD function enable										
MB88155-400							-1.0%, -2.0% no modulation	PD function disable	8P	-								
MB88155-402						Down	-1.0%, -2.0%	PD function enable										
MB88155-410		3.3	12.5 to 20	× 4	50 to 80		±0.5%, ±1.0% no modulation	PD function disable										
MB88155-412		± 0.3	20 to 28 (×1) 14 to 40 (×2)		Center		±0.5%, ±1.0%	PD function enable										
MB88156-000				×1, ×2,	20 to 28 (× 1)		-1.0%, -2.0%, ±0.5%,	REFoutput enable										
MB88156-001	EMI noise			(selection)	Down/ Center	\pm 1.0%, no modulation	REFoutput disable		16P									
MB88161	reduction PLL (SSCG)		$\begin{array}{c} 12 \text{ to } 28 \\ (\times 1) \\ 20 \text{ to } 42 \\ (\times 4) \end{array}$	\times 1, \times 4, (selection)	12 to 28 (× 1) 80 to 168 (× 4)	(selection)	-1.0%, -2.0%, -4.0%, ±0.5%, ±1.0%, ±2.0%, no modulation	PD function enable	-	18P								
MB88162											12 to 28 (×1) 20 to 42 (×4)	\times 1, \times 4, (selectable)	12 to 28 (× 1) 80 to 168 (× 4)	Down/ Center (selectable)	-1.0%, -2.0%, -4.0%, ±0.5%, ±1.0%, ±2.0%, no modulation	PD function enable	-	18P
⊚ MB88163			12.5 to 26		12.5 to 26		±0.5%, no modulation	-	-	6P								
⊚ MB88163-100				× 1	20 to 42													
© MB88163-200		1.8 ± 0.15	20 to 42	× 2	40 to 84	Center	±0.25%, ±0.5%,	OE	- 5									
⊚ MB88163-400			× 4 80 to 168			±1.0%, no modulation	function enable	89	-									
© MB88163-500			12.5 to 26	× 1	12.5 to 26													
MB88181		3.3 ± 0.3	16 to 32	× 1/2 or more *	8 to 166	Center	±0.5%, ±1.0%, ±1.5%, ±2.0%, no modulation	PD function enable, Clock output 8(Max.)	20P	-								

*: The efficiency of multiply and the output mode can be arbitrarily set by the mask option.

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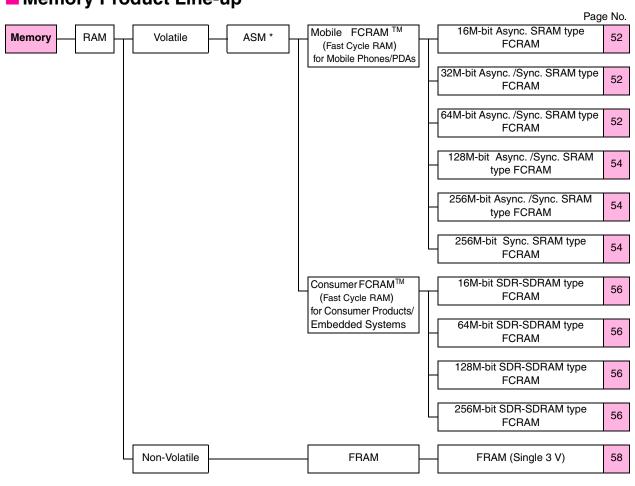
Package: P - Plastic

Spread Spectrum Clock Generator

SSCG Simple Evaluation Board

	Part number	R	lemarks
	MB88151AEB01-100	MB88151A-100 mounted	
	MB88151AEB01-101	MB88151A-101 mounted	
	MB88151AEB01-200	MB88151A-200 mounted	
	MB88151AEB01-201	MB88151A-201 mounted	
	MB88151AEB01-400	MB88151A-400 mounted	
MB88151A	MB88151AEB01-401	MB88151A-401 mounted	
	MB88151AEB01-500	MB88151A-500 mounted	
	MB88151AEB01-501	MB88151A-501 mounted	
	MB88151AEB01-800	MB88151A-800 mounted	
	MB88151AEB01-801	MB88151A-801 mounted	
	MB88152AEB01-100	MB88152A-100 mounted	
	MB88152AEB01-110	MB88152A-110 mounted	
MB88152A	MB88152AEB01-101	MB88152A-101 mounted	
MD00152A	MB88152AEB01-111	MB88152A-111 mounted	
	MB88152AEB01-102	MB88152A-102 mounted	
	MB88152AEB01-112	MB88152A-112 mounted	
	MB88153AEB01-100	MB88153A-100 mounted	
MB88153A	MB88153AEB01-101	MB88153A-101 mounted	
MD00155A	MB88153AEB01-110	MB88153A-110 mounted	
	MB88153AEB01-111	MB88153A-111 mounted	
	MB88154AEB01-102	MB88154A-102 mounted	
MB88154A	MB88154AEB01-103	MB88154A-103 mounted	An oscillation vibrator, oscillation
WID00154A	MB88154AEB01-112	MB88154A-112 mounted	stable capacity, and a power supply
	MB88154AEB01-113	MB88154A-113 mounted	line are required.
	MB88155EB01-100	MB88155-100 mounted	
	MB88155EB01-101	MB88155-101 mounted	
	MB88155EB01-102	MB88155-102 mounted	
	MB88155EB01-103	MB88155-103 mounted	
	MB88155EB01-110	MB88155-110 mounted	
MB88155	MB88155EB01-111	MB88155-111 mounted	
MD00133	MB88155EB01-112	MB88155-112 mounted	
	MB88155EB01-113	MB88155-113 mounted	
	MB88155EB01-400	MB88155-400 mounted	
	MB88155EB01-402	MB88155-402 mounted	
	MB88155EB01-410	MB88155-410 mounted	
	MB88155EB01-412	MB88155-412 mounted	
MB88156	MB88156EB01-BC16-000	MB88156-000 mounted	
	MB88156EB01-BC16-001	MB88156-001 mounted	
MB88161	MB88161EB01	MB88161 mounted	
MB88162	MB88162EB01	MB88162 mounted	
	©MB88163EB01	MB88163 mounted	
	©MB88163EB01	MB88163-100 mounted	
MB88163	©MB88163-200EB02	MB88163-200 mounted	
	©MB88163-400EB02	MB88163-400 mounted	
	©MB88163-500EB02	MB88163-500 mounted	

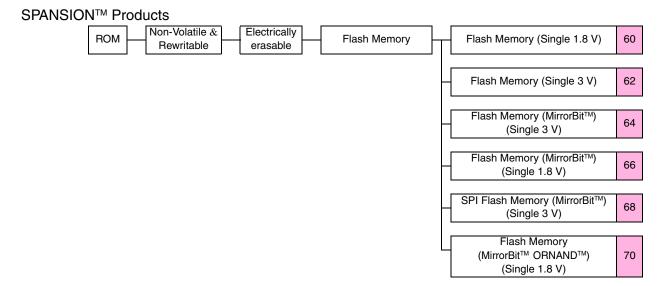
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Memory Product Line-up

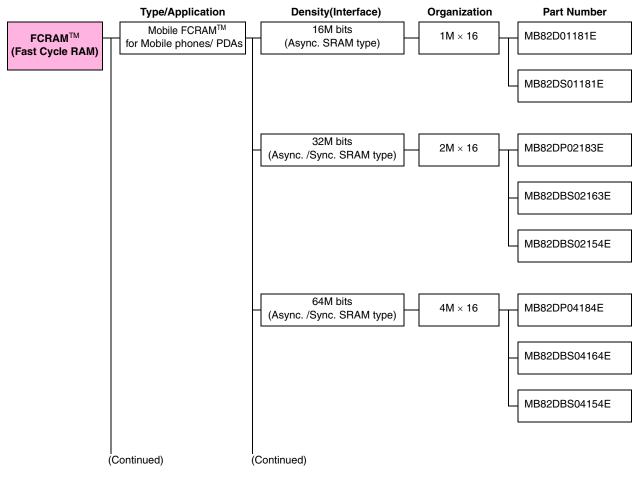
* : ASM = Application Specific Memory

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MirrorBit is a trademark of Spansion Inc. ORNAND is a trademark of Spansion Inc.

FCRAM[™] (Fast Cycle RAM) (1)



FCRAM is a trademark of Fujitsu Microelectronics Limited.

■ Mobile FCRAMTM (Fast Cycle RAM)

• 16M-bit Async. SRAM Type FCRAM

				Page Mode	Burst Mode	Burst Clock	Supply	Current	Max.	Supply
	Organization (W × b)	Part Number	Access Time Max. (ns)	Access Time Max. (ns)	Frequency Max (MHz)	Access Time Max. (ns)	Time Operating Standby Do Max. (ns) (mA) (μA) (μA)		Power Down (μΑ)	Voltage (V)
	1M × 16	MB82D01181E-60L *1	60	N/A	N/A	N/A	20	100 * ³	10	2.3 to 3.5
_		MB82DS01181E-70L *2	70	N/A	N/A	N/A	20	100	10	1.7 to 1.95

*1: Shipping form: Chip, wafer, 48-pin FBGA package (SRAM compatible pinout)

*2: Shipping form: Chip, wafer

Package support for mass production is T.B.D.

*3: At V_{DD} ≤ 3.1V

• 32M-bit Async. /Sync. SRAM Type FCRAM

Initial Supply Current Max. Page Mode Burst Clock Access Burst Mode Organization Supply Access Access Power Time Part Number Frequency Operating Standby (W × b) Time Time Voltage (V) Max. (MHz) Down Max. (mA) (μA) Max. (ns) Max. (ns) (μ**Α**) (ns) *4 MB82DP02183E-65L 65 20 N/A N/A 30 120 10 2.6 to 3.1 8 *⁵ $2M \times 16$ 70 20 83 30 120 10 1.7 to 1.95 MB82DBS02163E-70L 70 N/A 104 7 *6 30 120 10 1.7 to 1.95 MB82DBS02154E-70L *1: Compliant with COSMORAM spec

*2: MB82DP02183E : with Page mode

MB82DBS02163E : with SDR Burst mode & Page mode

MB82DBS02154E : with SDR Burst mode & Multiplexed Address and Data Bus

*3: Shipping form: Chip, wafer, 71-pin FBGA package

- *4: At asynchronous operation
- *5: At RL = 5, 6
- *6: At RL = 7

• 64M-bit Async. /Sync. SRAM Type FCRAM

*1, *2, *3

*1, *2, *3

			Page Mode	e Burst Mode	Burst Clock	Supply	Curren	t Max.	Supply
Organization (W × b)	Part Number	Access Time Max. (ns) * ⁴	Access Time Max. (ns)	Frequency	Access Time Max. (ns)	Operating (mA)	Standby (μA)	Power Down (μΑ)	Voltage (V)
	MB82DP04184E-65L	65	20	N/A	N/A	40	200	10	2.6 to 3.1
4M imes 16	MB82DBS04164E-70L	70	20	104	7 * ⁵	40	200	10	1.7 to 1.95
	MB82DBS04154E-70L	70	N/A	104	7 * ⁵	40	200	10	1.7 to 1.95

*1: Compliant with COSMORAM spec

*2: MB82DP04184E : with Page mode

MB82DBS04164E : with SDR Burst mode & Page mode

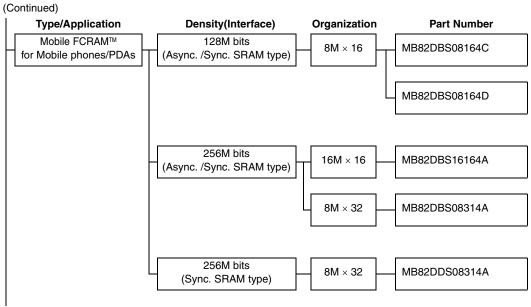
MB82DBS04154E : with SDR Burst mode & Multiplexed Address and Data Bus *3: Shipping form: Chip, wafer

Package (71-pin FBGA) support for mass production is T.B.D.

*4: At asynchronous operation

*5: At RL = 6, 7

FCRAM[™] (Fast Cycle RAM) (2)



(Continued)

FCRAM is a trademark of Fujitsu Microelectronics Limited.

• 128M-bit Async. /Sync. SRAM Type FCRAM

	Initial Page Mode		Burst Mode	Burst Clock	Supply	Current	Max.	Supply	
Organization (W × b)	Part Number	Access Time Max. (ns) * ³	Access Time Max. (ns)	Frequency	Access Time Max. (ns)	Operating (mA)	Standby (μΑ)	Power Down (µA)	Voltage (V)
8M × 16	MB82DBS08164C-70L	70	N/A	104	6 * ⁴	40	300	10	1.7 to 1.95
	O MB82DBS08164D-70L	70	N/A	104	6 * ⁴	35 * ⁵	200	10	1.7 to 1.95

O: New Product

*1: Compliant with COSMORAM spec, with SDR Burst mode

*2: Shipping form: Chip, wafer

Package support for mass production is T.B.D.

*3: At asynchronous operation

*4: At RL = 6, 7

*5: T_A <u>≤</u> +40 °C

• 256M-bit Async. /Sync. SRAM Type FCRAM

			Page Mode	Burst Mode	Burst Clock	Supply	Current	Max.	Supply	
Organization (W × b)	Part Number	Access Time Max. (ns) * ³ Access Time Max. (ns)		Frequency	Access Time Max. (ns)	Operating (mA)	Standby (μA)	Power Down (μΑ)	Voltage (V)	
16M imes 16	MB82DBS16164A-80L	80	N/A	100	7 *4	40	250 * ⁵	10	1.7 to 1.95	
$8M \times 32$	MB82DBS08314A-80L	80	N/A	100	7 *4	40	250 * ⁵	10	1.7 to 1.95	

*1: Compliant with COSMORAM spec, with SDR Burst mode

*2: Shipping form: Chip, wafer

Package(115-pin FBGA) support for mass production is T.B.D.

- *3: At asynchronous operation
- *4: At RL = 7, 8
- *5: T_A <u>≤</u> +40 °C

• 256M-bit Sync. SRAM Type FCRAM

Supply Current Max. Initial Burst Clock Page Mode Supply Burst Mode Access Organization Access Access Power Voltage Frequency Part Number Standby Operating Time Time Time (W × b) Down Max. (MHz) (V) Max. (ns) Max. (ns) (mA) (µA) Max. (ns) *³ (μA) 1.75 to 6 *⁴ 250 *5 $8M \times 32$ MB82DDS08314A-75L 45 N/A 135 40 10 1.95

*1: Compliant with COSMORAM spec, with DDR Burst mode & Multiplexed Address and Data Bus

*2: Shipping form: Chip, wafer

Package(115-pin FBGA) support for mass production is T.B.D.

- *3: At Burst mode
- *4: Data access time from CLK, CLK
- *5: T_A <u>≤</u> +40 °C

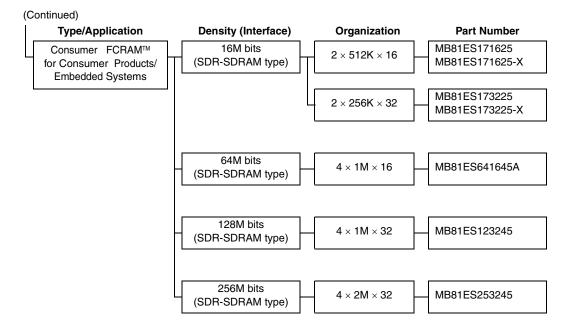
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FCRAM[™] (Fast Cycle RAM) (3)



FCRAM is a trademark of Fujitsu Microelectronics Limited.

■ Consumer FCRAMTM (Fast Cycle RAM)

• 16M-bit SDR-SDRAM Type FCRAM

	51						*1, *2	
Organization		Clock	Clock Period	Access Time	Supply Curre	ent Max. * ⁵	Supply	
$(Bank \times W \times b)$	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * ⁴	Operating (mA)	Standby (mA)	Voltage (V)	
	MB81ES171625-12	85	11.7	10.2	30	1	1.65 to 1.95	
$2\times512K\times16$	MB81ES171625-15	66.7	15	12	30	1	1.65 to 1.95	
	MB81ES171625-15-X * ³	66.7	15	12	30	1	1.65 to 1.95	
	MB81ES173225-12	85	11.7	10.2	30	1	1.65 to 1.95	
$2\times256K\times32$	MB81ES173225-15	66.7	15	12	30	1	1.65 to 1.95	
	MB81ES173225-15-X * ³	66.7	15	12	30	1	1.65 to 1.95	

*1: Single Data Rate SDRAM Interface

*2: Shipping form: Chip, wafer

*3: Extended operating temperature

*4: Access Time = t_{AC} *5: Operating current is I_{DD1} (1 bank active) and Standby current is I_{DD2P} (Power down mode)

64M-bit SDR-SDRAM Type FCRAM

Organization		Clock	Clock Period	Access Time	Supply Cur	rent Max.	Supply
(Bank \times W \times b)	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * ³	Operating (mA)	Standby (mA)	Voltage (V)
$4\times1M\times16$	O MB81ES641645A-07	135	7.4	6.5	T.B.D.	T.B.D.	1.7 to 1.95

○: New Product

*1: Single Data Rate SDRAM Interface

*2: Shipping form: Chip, wafer, 54-pin FBGA package

*3: Access Time = t_{AC}

128M-bit SDR-SDRAM Type FCRAM

Organization		Clock	Clock Period	Access Time	Supply Curr	ent Max. * ⁴	Supply
(Bank × W × b)	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * ³	Operating (mA)	Standby (mA)	Voltage (V)
$4\times1M\times32$	MB81ES123245-10	108	9.2	7	*5	0.5	1.7 to 1.9

*1: Single Data Rate SDRAM Interface

*2: Shipping form: Chip, wafer

*3: Access Time = t_{AC}

*4: Operating current is I_{DD1} (1 bank active) and Standby current is I_{DD2P} (Power down mode)

*5: 60 (256 page length), 45 (128 page Length), 35 (64 page length)

256M-bit SDR-SDRAM Type FCRAM

							*1, *2
Organization		Clock	Clock Period	Access Time	Supply Cur	rent Max.	Supply
(Bank \times W \times b)	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * ³	Operating (mA)	Standby (mA)	Voltage (V)
$4\times 2M\times 32$	© MB81ES253245	166	6	6	T.B.D.	T.B.D.	1.7 to 1.95

©: Under development

*1: Single Data Rate SDRAM Interface

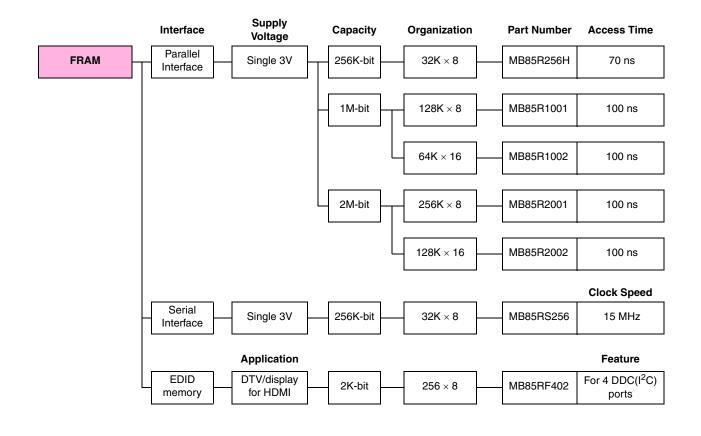
*2: Shipping form: Chip, wafer

*3: Access Time = t_{AC}

*1 *2

*1 *0

FRAM (Ferroelectric RAM)



FRAM

	Organization		Access Time		Clock Speed					Supply			Packages		
Interface	(W × b)	Part Number	Max. (ns)	Min. (ns)		Operating Standby		Voltage (V)	Range T _A (°C)	SOP	TSOP	FBGA			
Parallel	32K × 8	MB85R256H	70	150	-	5	5	2.7 to 3.6	-40 to +85	28P	28P	-			
Parallel	128K × 8	MB85R1001	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	-			
Parallel	64K × 16	MB85R1002	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	48P			
Parallel	256K × 8	MB85R2001	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	-			
Parallel	128K × 16	MB85R2002	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	-			
Serial	32K × 8	MB85RS256	-	1	15	5	3	3.0 to 3.6	-20 to +85	8P	-	-			

Pakage : P - Plastic

EDID memory

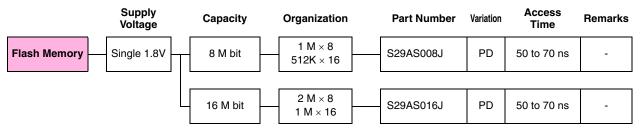
Part Number	Memory	Organization (W \times b)	Interface	Supply Voltage (V)	Packages TSSOP
O MB85RF402	FRAM	256 × 8	For 4 DDC(I ² C) ports	3.8 to 5.5	16P
		Delesso D Disstis			

○ : New released.

Pakage : P – Plastic

Flash Memory (Single 1.8V)

SPANSION[™] Products



SPANSION[™] Products

Flash memory (Single 1.8V)

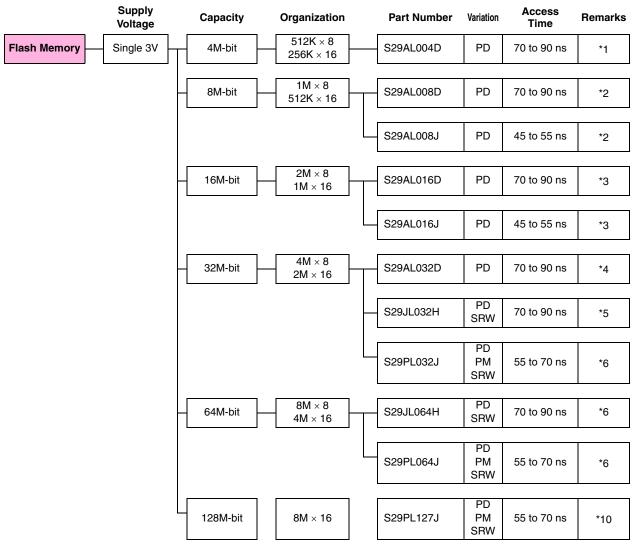
		Access	Cycle	V _{CC} Current		V _{CC} Current		V _{CC} Current			Operating	Packages	
Organization (W × b)	Part Number	Time Max. (ns)	Time Min. (ns)	Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T _A (°C)	TSOP	FBGA				
1 M × 8		50	50	16	5	1.65 to 1.95	-40 to +85	48P	48P				
512 K × 16	◎ S29AS008J70	70	70	(f = 5 MHz)	5	1.05 to 1.95	-40 10 +65	40F	401				
2 M × 8		50	50	16	5	1.65 to 1.95	-40 to +85	48P	48P				
1 M × 16	© S29AS016J70	70	70	(f = 5 MHz)	5	1.05 10 1.95	-40 10 +65	401	401				

☺: Under Developing

Package: P-Plastic

Flash Memory (Single 3V)

SPANSION[™] Products



Variation PD: Automatic sleep mode PM: Page mode SRW: Simultaneous Read / Write operation (Read-while-program or Readwhile-Erase)

MirrorBit is a trademark of Spansion Inc.

```
*1: (16Kbytes × 1sectors) + (8Kbytes × 2sectors) + (32Kbytes × 1sector) + (64Kbytes × 7sectors)
```

```
*2: (16Kbytes × 1sectors) + (8Kbytes × 2sectors) + (32Kbytes × 1sector) + (64Kbytes × 15sectors)
```

```
*3: (16Kbytes × 1sectors) + (8Kbytes × 2sectors + (32Kbytes × 1sector) + (64Kbytes × 31sectors)
```

```
*4: (16Kbytes × 1sectors) + (8Kbytes × 2sectors + (32Kbytes × 1sector) + (64Kbytes × 61sectors)
```

```
*5 : (8Kbytes × 8sectors) + (64Kbytes × 63sectors)
```

```
*6 : (8Kbytes × 16sectors) + (64Kbytes × 126sectors)
```

```
*7 : (8Kbytes × 8sectors) + (64Kbytes × 127sectors)
```

```
*8 : (64Kbytes × 128sectors)
```

```
*9 : (8Kbytes × 16sectors) + (64Kbytes × 62sectors)
```

```
*10: (8Kbytes × 16sectors) + (64Kbytes × 254sectors)
```

SPANSION[™] Products

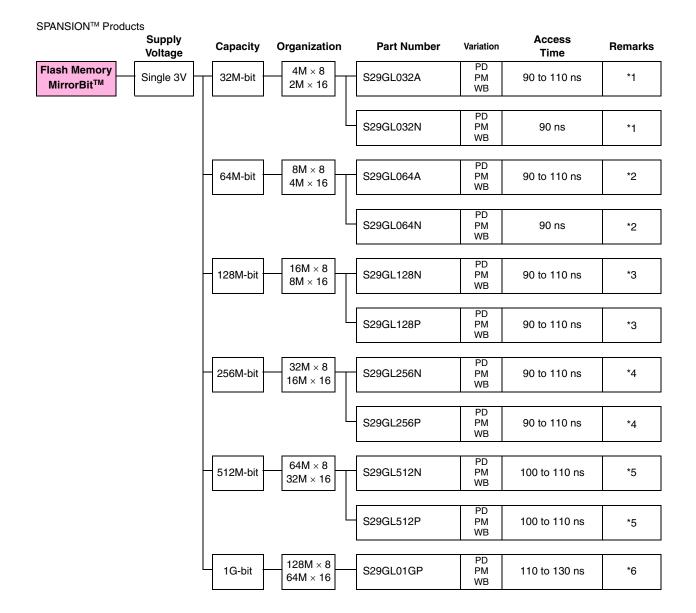
Flash memory (Single 3V)

		Access	Cycle	V _{CC} Cu	rrent		Operating		ackage	s
Organization (W × b)	Part Number	Time Max. (ns)	Cycle Time Min. (ns)	Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T _A (°C)		FBGA	SOP
512K × 8	S29AL004D70 *	70	70	16	5	2.7 to 3.6	-40 to +85	48P	48P	44P
256K × 16	S29AL004D90	90	90	(f = 5 MHz)	5	2.7 10 3.0	-40 10 +65	405	407	446
	S29AL008D70 *	70	70	16	5	2.7 to 3.6	-40 to +85	48P	48P	44P
1M × 8	S29AL008D90	90	90	(f = 5 MHz)	5	2.7 10 3.0	-40 10 +85	405	407	446
512K × 16	© S29AL008J45	45	45	16	F	0.7 to 0.6	40 to 195	48P	48P	44P
	© S29AL008J55	55	55	(f = 5 MHz)	5	2.7 to 3.6	-40 to +85	468	402	442
	S29AL016D70 *	70	70	16	F	0.7 to 0.6	40 to 195	400	400	
2M × 8	S29AL016D90	90	90	(f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48P	48P	_
$1M \times 16$	© S29AL016J45	45	45	16	_	0.710.0.0	40 to 195	400	48P	445
	© S29AL016J55	55	55	(f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48P	48P	44P
	S29AL032D70 *	70	70	16	_	0.710.00	40.1-05	400	40.0	400
	S29AL032D90	90	90	(f = 5 MHz)	(f = 5 MHz) 5	2.7 to 3.6	-40 to +85	48P	48P	48P
	S29JL032H70	70	70	16	F	0.7 to 0.6	40 to 195	48P		
4M imes 8	S29JL032H90	90	90	(f = 5 MHz)	5	2.7 to 3.6	-40 to +85	468	-	_
$2M \times 16$	S29PL032J55	55	55		5					
	S29PL032J60	60	60	30		2.7 to 3.6	-45 to +85	_	48P	
	S29PL032J65	65	65	(f = 5 MHz)	5				56P	_
	S29PL032J70	70	70							
	S29JL064H70	70	70	16	5	2.7 to 3.6	-40 to +85	48P	-	
	S29JL064H90	90	90	(f = 5 MHz)	5	2.7 10 3.0	-40 10 +85	401	-	_
8M × 8	S29PL064J55	55	55							
$4M \times 16$	S29PL064J60	60	60	30	5	2.7 to 3.6	-45 to +85		48P	
	S29PL064J65	65	65	(f = 5 MHz)	5	2.7 10 3.0	-45 10 +85	-	56P	_
	S29PL064J70	70	70							
	S29PL127J55	55	55			2.7 to 3.6				
8M × 16	S29PL127J60	60	60	30	5	2.7 10 3.0	-45 to +85	56P	50P	
	S29PL127J65	65	65	(f = 5 MHz)	5	2.7 to 3.6	-40 IU +00	50F	50F	_
	S29PL127J70	70	70			1.65 to 1.95				

©: Under Developing

^{* :} at C_L = 30pF

Flash Memory (MirrorBit[™]) (Single 3 V)



Variation
PD : Automatic sleep mode
PM: Page mode
WB: Write buffer

MirrorBit is a trademark of Spansion Inc.

*1: Uniform sector model : 32Kword (64Kbytes) × 64sectors

Boot sector model : 32Kword (64Kbytes) × 63sectors + 4Kword (8Kbytes) × 8sectors

- *2: Uniform sector model : 32Kword (64Kbytes) × 128sectors
- Boot sector model : 32Kword (64Kbytes) × 127sectors + 4Kword (8Kbytes) × 8sectors
- *3: Sector structure 64Kword (128Kbytes) × 128sectors
- *4: Sector structure 64Kword (128Kbytes) \times 256sectors
- *5: Sector structure 64Kword (128Kbytes) \times 512sectors
- *6: Sector structure 64Kword (128Kbytes) × 1024sectors

SPANSION[™] Products

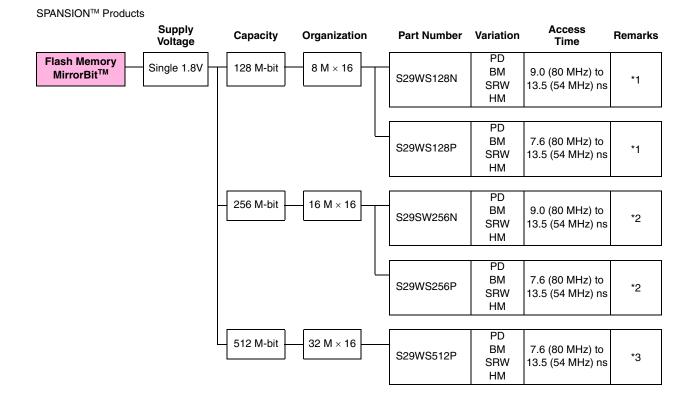
Flash memory (MirrorBit) (Single 3V)

		Access	Cycle	V _{CC} Cu	rrent		Operating	Pack	ages
Organization (W × b)	Part Number	Time Max. (ns)	Time Min. (ns)	Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T _A (°C)	TSOP	FBGA
	S29GL032A90	90 (25)	90					40P	
4M × 8	S29GL032A10	100 (30)	100	25 (f = 5 MHz)	5	3.0 to 3.6	-40 to +85	48P 56P	48P 64P
2M × 16	S29GL032A11	110 (30)	110					30F	
	S29GL032N90	90 (25)	90	40 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48P 56P	48P 56P
	S29GL064A90	90 (25)	90						
8M × 8	S29GL064A10	100 (30)	100	25 (f = 5 MHz)	5	3.0 to 3.6	-40 to +85	48P 56P	64P
4M × 16	S29GL064A11	110 (30)	110						
	S29GL064N90	90 (25)	90	40 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48P 56P	48P 56P
	S29GL128N90	90 (25)	90			3.0 to 3.6			
	S29GL128N10	100 (25)	100	50 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56P	64P
16M × 8	S29GL128N11	110 (30)	110	. ,		2.7 10 0.0			
8M × 16	S29GL128P90	90 (25)	90	50		3.0 to 3.6	0 to +70 -40 to +85		
	S29GL128P10	100 (25)	100	(f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56P	64P
	S29GL128P11	110 (25)	110			2.7 10 0.0	40 10 100		
	S29GL256N90	90 (25)	90	50	l	3.0 to 3.6			
	S29GL256N10	100 (25)	100	50 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56P	64P
32M × 8	S29GL256N11	110 (30)	110			2.7 10 0.0			
16M × 16	S29GL256P90	90 (25)	90	50		3.0 to 3.6	0 to +70 -40 to +85		
	S29GL256P10	100 (25)	100	(f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56P	64P
	S29GL256P11	110 (25)	110			2.7 10 0.0	40 10 400		
	S29GL512N10	100 (25)	100	50	5	2.7 to 3.6	-40 to +85	56P	64P
	S29GL512N11	110 (30)	110	(f = 5 MHz)	Ŭ	2.7 10 0.0		001	011
64M × 8 32M × 16	S29GL512P10	100 (25)	100	50		3.0 to 3.6	0 to +70 -40 to +85		
	S29GL512P11	110 (25)	110	(f = 5 MHz)	5	2.7 to 3.6	-40 to +85	56P	64P
	S29GL512P12	120 (25)	120						
128M × 8	S29GL01GP11	110 (25)	110	50		3.0 to 3.6	0 to +70 -40 to +85		
64M × 16	S29GL01GP12	120 (25)	120	(f = 5 MHz)	5	2.7 to 3.6		56P	64P
	S29GL01GP13	130 (25)	130			2.7 10 0.0			

Memory

C_L = 30pF Package: P-Plastic

Flash Memory (MirrorBit[™]) (Single 1.8V)



Variation	
PD: Automatic sleep mode	
BM: Burst mode	
SRW: Simultaneous Raad/Write operation	
(Read-while-program or Read-while-Erase)	
HM: Hand Shake Mode	

- *1 : 16 Kword \times 8sectors + 64 Kword \times 126sectors
- *2 : 16 Kword \times 8sectors + 64 Kword \times 254sectors
- *3 : 16 Kword \times 8sectors + 64 Kword \times 510sectors

MirrorBit is a trademark of Spansion Inc.

SPANSION[™] Products

Flash memory (MirrorBit) (Single 1.8V)

Organization (W × b)	Part Number	Access Time Max. (ns)	Burst Speed (MHz)	V _{CC} Current			Operating	Packages
				Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T _A (°C)	FBGA
8 M × 16	S29WS128N0LBxW	80 * ¹ 80/13.5 * ²	54	36 * ³	70	1.70 to 1.95	-25 to +85	84P
	S29WS128N0PBxW	80 * ¹ 80/11.2 * ²	66	42 * ³				
	S29WS128N0SBxW	80 * ¹ 80/9.0 * ²	80	48 * ³				
	S29WS128P0LBxW	80 * ¹ 80/13.5 * ²	54	39 * ³				
	S29WS128P0PBxW	80 * ¹ 80/11.2 * ²	66	43 * ³				
	S29WS128P0SBxW	80 * ¹ 80/9.0 * ²	80	48 * ³				
	S29WS128PABBxW	80 * ¹ 80/7.6 * ²	108	54 * ³				
16 M × 16	S29WS256N0LBxW	80 * ¹ 80/13.5 * ²	54	36 * ³	70	1.70 to 1.95	-25 to +85	84P
	S29WS256N0PBxW	80 * ¹ 80/11.2 * ²	66	42 * ³				
	S29WS256N0SBxW	80 * ¹ 80/9.0 * ²	80	48 * ³				
	S29WS256P0LBxW	80 * ¹ 80/13.5 * ²	54	39 * ³				
	S29WS256P0PBxW	80 * ¹ 80/11.2 * ²	66	43 * ³				
	S29WS256P0SBxW	80 * ¹ 80/9.0 * ²	80	48 * ³				
	S29WS256PABBxW	80 * ¹ 80/7.6 * ²	108	54 * ³				
32 M × 16	S29WS512P0LBxW	80 * ¹ 80/13.5 * ²	54	36 * ³	70	1.70 to 1.95	-25 to +85	84P
	S29WS512P0PBxW	80 * ¹ 80/11.2 * ²	66	43 * ³				
	S29WS512P0SBxW	80 * ¹ 80/9.0 * ²	80	48 * ³				
	S29WS512PABBxW	80 * ¹ 80/7.6 * ²	108	54 * ³				

 $C_L = 30 pF$

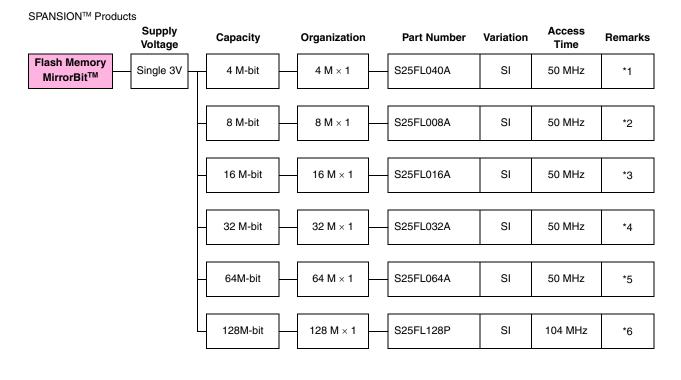
Package: P-Plastic

*1: Asynchronous access time

*2: Synchronous delay time/burst access time

*3: At burst read Continuous mode (Max.)

Serial Peripheral Interface (MirrorBit[™]) (Single 3V)



Variation SI: Serial interface

*1 : Sector structure - 512 K bits \times 8 sectors or 128 K bits \times 2 sectors + 32 K bits \times 2 sectors + 16 K bits \times 2 sectors + 512 K bits \times 7 sectors

- *2 : Sector structure 512 K bits \times 16 sectors
- *3 : Sector structure 512 K bits \times 32 sectors
- *4 : Sector structure 512 K bits \times 64 sectors

*5 : Sector structure - 512 K bits \times 128 sectors

*6 : Sector structure - 512 K bits \times 256 sectors

MirrorBit is a trademark of Spansion Inc.

SPANSION[™] Products

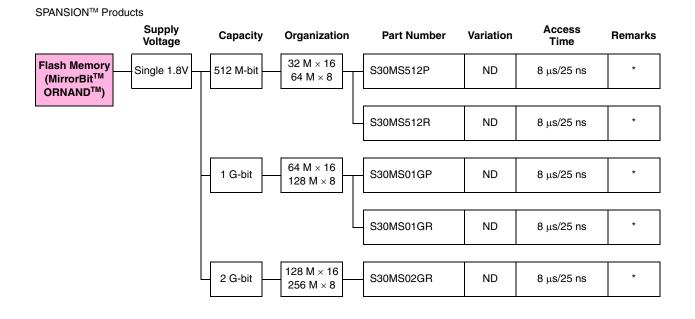
Flash memory (MirrorBit) (Single 3V)

Organization	Part Number	Clock	V _{CC} Current		Supply	Operating Temperature	Packages	
(W × b)		speed (MHz)	Read (mA)	Standby Mode (µA)	Voltage (V)	Range T _A (°C)	SOIC	SON
$4 \text{ M} \times 1$	S25FL040A	50	13 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC8	USON8
8 M × 1	S25FL008A	50	13 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC8	USON8
16 M × 1	S25FL016A	50	19 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC8 SOIC16	WSON8
32 M × 1	S25FL032A	50	19 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC16	-
64 M × 1	S25FL064A	50	13 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC16	_
128 M × 1	S25FL128P	104	22 (f = 104MHz)	200	2.7 to 3.6	-40 to +85	SOIC16	WSON

 $C_L = 30 pF$

Package: P-Plastic

Flash Memory (MirrorBit[™] ORNAND[™]) (Single 1.8V)



Variation ND: NAND interface

* : Block size 128 K + 4 Kbyte

MirrorBit is a trademark of Spansion Inc. ORNAND is a trademark of Spansion Inc. SPANSION[™] Products

Flash memory (MirrorBit ORNAND) (Single 1.8V)

		Page	Serial	V _{CC} Current			Operating	Packages	
Organization (W × b)	Part Number	Access (μs)	Read (ns)	Read (mA)	Standby Mode (μA)	Supply Voltage (V)	Temperature Range T _A (°C)	TSOP	BGA
	S30MS512P25BFW00	8	25	45					137P
$64 \text{ M} \times 8$	S30MS512P25TFW00	8	25			1.70 to 1.95	-25 to +85	105	10/1
	O S30MS512R25TFW00	8	30	50	- 60	1.70 10 1.95	-25 10 +85	48P	
	O S30MS01GR25TFW01	8	30	50					-
-	S30MS512P25BFW01	8	25	45	60	1.70 to 1.95	-25 to +85	48P	137P
32 M imes 16	S30MS512P25TFW01	8	25						1375
	O S30MS512R25TFW01	8	30	50					-
	S30MS01GP25BFW00	8	25	45	- 60	1.70 to 1.95	-25 to +85	48P	137P
128 M × 8	S30MS01GP25TFW00	8	25	40					15/1
120 IVI × 0	O S30MS01GR25TFW00	8	30	50				407	
	O S30MS02GR25TFW01	8	30	50					-
64 M × 16	S30MS01GP25BFW01	8	25	45	60	1.70 to 1.95	-25 to +85	48P	137P
	S30MS01GP25TFW01	8	25	40	00	1.70101.95			1377
$256 \text{ M} \times 8$	O S30MS02GR25TFW00	8	30	50	60	1.70 to 1.95	-25 to +85	48P	-

 $\bigcirc: \text{New Product}$

Package: P-Plastic

 $C_L = 30 pF$

The productions listed below are scheduled to go out of production. If you are considering the use in the new applications, select the other series of products

FCRAM

Part number	Description
MB82DP02183C-65L	32 Mbit Async. SRAM Type FCRAM
MB82DBS02163C-70L	32 Mbit Async./Sync. SRAM Type FCRAM
MB82DP04183C-65L	64 Mbit Async. SRAM Type
MB82DP04183D-65L	FCRAM
MB82DBS04163C-70L	64 Mbit Async./Sync. SRAM Type
MB82DBS04163D-70L	FCRAM
MB82DBS04314C-70L	128 Mbit Async./Sync. SRAM Type FCRAM

ASIC Product Line-up

ASIC Products

				Pag	e No
ASIC Products	Standard cell	CMOS	CS201 serie	es with on-chip RAM, ROM, ADC/DAC	74
			- CS101 serie	More than 91,000,000 (on-chip) gates with on-chip RAM, ROM, ADC/DAC	75
			CS91 serie	More than 48,000,000 (on-chip) gates with on-chip RAM, ROM, Multipliers, ADC/DAC	76
			CS86 serie	More than 40,000,000 (on-chip) gates with on-chip RAM, ROM, FIFO, Delay Line, ADC/DAC	77
			CS81 serie	More than 40,000,000 (on-chip) gates, 11 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	78
			CS66 serie	More than 1,700,000 (on-chip) gates, 98 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	79
	Macro-embedded type cell arrays	CMOS	CE81 serie	Maximum of 34,000,000 (on chip) gates, 12 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	81
			CE77 serie	Maximum of 10,000,000 (on chip) gates, 33 ps/gate with on-chip RAM, ROM, FIFO, Delay Line	82
			CE71 serie	Maximum of 8,096,000 (on chip) gates, 29 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	84
			CE66 serie	Maximum of 1,138,000 (on-chip) gates, 98 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC.	86
			CE61 serie	Maximum of 2,025,000 (on chip) gates, 85 ps/gate with on-chip RAM/ROM, Multipliers, ADC/DAC	88
	Gate arrays	Sea-of-Gate CMOS	CG61 serie	Maximum of 1,568,000 (on chip) gates, 85 ps/gate with on-chip RAM, Analog PLL embedment is possible in some frames	90
			CG47 serie	s Maximum of 55,000 (on chip) gates, 300 ps/gate with on-chip RAM, FIFO	91
			CG46 serie	Maximum of 198,000 (on chip) gates, 300 ps/gate with on-chip RAM, FIFO	92

CS201 Series

Features

Technology : 65 nm Si-gate CMOS 6- to 12-metal layers. Low-k (low permittivity) inter-layer insulation film material is used for all layers. Consolidation of all 3 kinds of set of cell (energy-saving version to high-velocity version) is possible. Supply voltage : +1.2 V \pm 0.1 V , +1.0 V \pm 0.1 V Junction temperature range : -40 °C to +125 °C Reduced chip sized realized by I/O with pad. Supports a wide range of cell sets (from low power versions to high speed versions) IP macros : CPU (ARM11, ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others Compiled cells (RAM/ROM and others) It supports energy-saving mode, multi mode SRAM. It supports energy-saving technology "CoolAdjust"* Supports large capacity memory (1T-SRAM-Q) High-speed interface macro (up to 10 Gbps) Special interfaces (LVDS, SSTL and others) Supports use of industry standard libraries (. LIB) Uses industry standard tools and supports the optimum tools for the application. High reliability design estimation in the early stage of physical design realized by physical prototyping tool. Layout synthesis with optimized timing realized by physical synthesis tools. Hierarchical design environment for supporting large-scale circuits. High accuracy design environment considering dynamic drop in power supply voltages, signal noise, delay penalty, and crosstalk. I/O design environment (power line design, assignment and selection of I/Os, package selection) considering noise. Supports static timing sign-off Improved timing settling by introducing Statistical Timing Analysis (SSTA). Steady product supply and countermeasure for diffusion by introduction of DFM Supports memory (RAM/ROM) BIST Supports boundary SCAN Supports LOGIC BIST Supports transition delay test Optimum of package lineup : TEBGA, FBGA, PBGA, FC-BGA *: "CoolAdjust" is a generic name of Fujitsu Microelectronics's energy-saving technology

CS101 Series

Features

Features	
Optimum gate count	: Maximum of 91,000,000 gates
Technology	: 90 nm Si-gate CMOS 6- to 10-metal layers. Low-k (low permittivity) inter-layer insulation film material is
	used for all layers.
	3 types of transistors (low leak, standard, high speed) can be mixed on a chip.
Supply voltage	The design rules comply with industry standard processes.
Supply voltage	: +1.2 V ± 0.1 V, +1.0 V ± 0.1 V ∋ : -40 °C to +125 °C (normal)
Gate delay time	
	: $Pd = 2.7 \text{ nW/MHz/BC} (1.2 \text{ V, Inverter, F/O} = 1)$
Reduced chip sized realize	
	ell sets (from low power versions to high speed versions)
IP macros	tandard design rules enables non-Fujitsu commercial macros to be easily incorporated. : CPU (ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others
Compiled cells (RAM/ROM	
High-speed interface macro	
Special interfaces (LVDS, S	SSTL_2 and others)
Supports use of industry st	
	Is and supports the optimum tools for the application.
	nation in the early stage of physical design realized by physical prototyping tool. nized timing realized by physical synthesis tools.
	ment for supporting large-scale circuits.
High accuracy design envir crosstalk.	ronment considering drop in power supply voltages, signal noise, delay penalty, and
	wer line design, assignment and selection of I/Os, package selection) considering noise.
Supports static timing sign-	
Supports memory (RAM/R	OM) BIST
Supports boundary SCAN	
Supports LOGIC BIST Supports transition delay te	est
Optimum of package lineup) : TEBGA, FBGA, PBGA, FC-BGA

CS91 Series

Features

Optimum gate count : Maximum of 48,000,000 gates Technology : 0.11 µm Si-gate CMOS, 5- to 8-layer wiring (Copper is used as wire material), Low-k Inter-laver material (Inter-layer material that has low permittivity) Supports 8 types of cell sets that differ in speed, integration, and power consumption. These cell sets can be mixed on a chip. : +1.2 V ± 0.1 V (normal) Supply voltage Junction temperature range : -40 to +125 °C tpd = 16 ps (1.2 V, Inverter, F/O = 1)Gate delay time : : Pd = 6.6 nW/MHz (1.2 V, Inverter, F/O = 1) Gate power consumption High-speed interface macro (up to 10 Gbps) Special interfaces: P-CML, LVDS, PCI, USB, SSTL, HSTL, T-LVTTL, and others Buffer cells for crystal oscillation circuits. : CPU (ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others IP macros Compiled cells (RAM/ROM/multiplier and others) Uses industry standard tools and supports the optimum tools for the application. Short-term development using a physical prototyping tool. Hierarchical design environment for supporting large-scale circuits. Supports Signal Integrity, EMI noise reduction Supports High resolution RC extraction base delay calculation environment Supports optimization environment of power supply wire Supports static timing sign-off Supports memory (RAM/ROM) BIST Supports boundary SCAN Supports LOGIC BIST Supports transition delay test A variety of package options : FC-BGA (Max. 2116 pin), EBGA, HQFP, FBGA and others

CS86 Series	
Features	
Optimum gate count Technology	 Maximum of 40,000,000 gates 0.18 μm Si-gate CMOS, 4- to 6-layer wiring Supports three types of internal cell sets (ultra high-speed, standard, low-leak) Capable of integrating a mixture of standard transistor cell and ultra high-speed pro- cess/cell, and mixture of standard transistor cell and low leak process/cell on a single
Cupply voltage	chip (-1.1.2)/(-0.15)/(normal) to (1.1)/(-0.1)/(-
Supply voltage Gate delay time	: $+1.8 V \pm 0.15V$ (normal) to $+1.1V \pm 0.1V$: tpd = 88 ps (standard : 1.8 V, 2NAND, F/O = 2, standard load) tpd = 70 ps (ultra high-speed : 1.8 V, 2NAND, F/O = 2, standard load) tpd = 136 ps (low-leak : 1.8 V, 2NAND, F/O = 2, standard load)
Leakage Current	: 0.023 nW (standard : 1.8 V, 2NAND, F/O = 0, no load) 3.922 nW (ultra high-speed : 1.8 V, 2NAND, F/O = 0, no load) 0.0067 nW (low-leak : 1.8 V, 2NAND, F/O = 0, no load)
Gate power consumption	: 40.1 nW/MHz (standard : 1.8 V, 2NAND, $F/O = 1$, 4Grid) 42.7 nW/MHz (ultra high-speed : 1.8 V, 2NAND, $F/O = 1$, 4Grid) 38.3 nW/MHz (low-leak : 1.8 V, 2NAND, $F/O = 1$, 4Grid)
Junction temperature range	
Output buffer cells with nois	
	III-up/pull-down resistors and bidirectional buffer cells.
Buffer cells for crystal oscill	
Special interfaces	: SSTL2, PCI, P-CML, T-LVTTL, USB2.0, IEEE1394, and others
IP macros	: CPU (FR-V, ARM9, and others), DSP, PCI, IEEE1394, USB2.0, IrDA, PLL, ADC, DAC,
Configurable internal bus c Advanced for hardware/sof Short-term development us Low-power dissipation usin Short-term development us Hierarchical design environ Supports signal Integrity Supports memory (RAM, R Supports memory (RAM) B Supports boundary SCAN Supports path delay test Supports transition delay test	tware co-design environment sing a physical synthesis tool g a low power synthesis tool sing a timing driven layout tool ment for supporting large-scale circuits ROM) SCAN BIST
A variety of package option	IS (QFP, TQFP, LQFP, HQFP, PBGA, FBGA, FLGA, EBGA)

Note: Some items are in preparation.

Packages The table below lists the available package types.

Туре	Pin Count	Material
QFP	176, 208, 240	Plastics
TQFP	100, 120	Plastics
LQFP	144, 176, 208, 256	Plastics
HQFP	208, 240, 256, 304	Plastics
PBGA	256, 352, 420	Plastics
FBGA	112, 144, 168, 176, 192, 224, 272, 288, 240, 304, 368	Plastics
FLGA	144, 176, 208, 224, 288	Plastics
EBGA	660	Plastics

Note: This list contains packages under planning. Contact Fujitsu Microelectronics for the availability.

CS81 Series

Features Optimum gate count : Maximum of 40,000,000 gates : 0.18 µm Si-gate CMOS, 3- to 6-layer wiring Technology Capable of integrating a mixture of high-speed processes and cells on a single chip Supply voltage : +1.8 V \pm 0.15V (normal) to +1.1V \pm 0.1V : tpd = 11 ps (1.8 V, Inverter, F/O = 1) Gate delay time Gate power consumption : 5nW/MHz/BC (1.1V, 2NAND, F/O = 1) Junction temperature range : -40 to +125 °C High-speed interface macro (up to 3.125 Gbps) Output buffer cells with noise reduction circuits Inputs with on-chip input pull-up/pull-down resistors (33 k Ω typical) and bidirectional buffer cells. Buffer cells for crystal oscillation circuits. Special interfaces: P-CML, LVDS, PCI, AGP, USB, SDRAM-I/F, SSTL, and others IP macros: CPU, DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others Compiled cells (RAM/ROM/multiplier, and others) Configurable internal bus circuits Advanced for hardware/software co-design environment Short-term development using a timing driven layout tool Supports static timing sign-off Dramatically reducing the time for generating test vectors for timing verification and the simulation time Hierarchical design environment for supporting large-scale circuits Simulation (before layout) considering the input through rate and high resolution RC extraction base delay calculation (after layout), supporting development with minimized timing trouble after trial manufacture. Supports signal Integrity, EMI noise reduction Supports memory (RAM, ROM) SCAN Supports memory (RAM) BIST Supports boundary SCAN Supports At-Speed test on internal circuits Supports path delay test Supports transition delay test A variety of package options (TQFP, HQFP, EBGA, FBGA, TAB-BGA, FC-BGA, LQFP)

Note: Some items are in preparation.

Packages

The table below lists the available package types.

Туре	Pin Count	Material
TAB-BGA	304, 352, 480 560, 660, 720	Plastics
EBGA	576, 660, 672	Plastics
HQFP	208, 240, 256, 304	Plastics
TQFP	100, 120	Plastics
LQFP	144, 176, 208	Plastics
FBGA	288	Plastics
FC-BGA	1089, 1225, 1369, 1681, 1849, 2116	Plastics, Ceramic

Note: This list contains packages under planning. Contact Fujitsu Microelectronics for the availability.

CS66 Series

Features

Γ	eatures	
	Optimum gate count Technology	: Maximum of 1,700,000 gates : 0.35 μm Si-gate, 3- to 4-layer metal wiring
	Supply voltage	: +3.3 V \pm 0.3 V (normal) to +2.0 V \pm 0.1 V +5.0 V \pm 10% (only for external interface; when internal requirements is 3.3 V) +3.3 V \pm 10% (only for external interface; when internal requirements is 3.3 to 2.0 V)
	Gate delay time	: t _{pd} = 91 ps (high-speed type, F/O = 2, standard load)
	Gate power consumption Junction temperature range	: 0.29 μW/MHz (F/O = 2, standard load) : -40 to +125°C
		: I _{OL} = 2 mA/4mA/8mA/12mA/24mA mixable.
	Output buffer cells with noise	
	On-chip input pull-up/pull-do	
	Buffer cells for crystal oscilla Configurable internal bus cir	
		//multipliers mountable; arbitrary words/bits configurable.
	Clock skew layout design me	ethod (Cadence "CT-Gen") based on the floor plan information minimizes post-layout
		g turnaround time for development.
		onsidering the input through rate and detailed RC delay calculation (after layout), h minimized timing trouble after trial manufacture.
		and SDRAM-I/F, and others)
	Analog PLL	
	Analog circuits (ADC, DAC,	
	Supports DFF scan test with	CPU core, CPU peripheral, operation macro, and others)
	Supports memory (RAM/RC	
	Supports memory (RAM) BI	,
	Supports boundary SCAN	
	Note: Some items are in pre	paration.

Number of gates used in each package The table below lists the available package types and the reference number of gates used. CS66 (P-frame)

ackage cou	and pin Int	0 2000K 4000K 6000K 8000K 10000K 12000K 14000K	16000K
TQFP	100		— 1579K
LQFP	100 144 176 208	1305K	— 1579K — 1579K — 1579K
QFP	120 144 160 176 208 240 256		 1579K
HQFP	208 240 256 304		1579K 1579K 1579K 1579K 1579K
PBGA	256 352		— 1579K — 1579K
FBGA	112 144 168 176 192 224 288	639K 639K 835K 1305K	— 1579K — 1579K — 1579K

CS66 (S-frame)

Package cou		0 100K 200K 300K 400K 500K 600K 700K	800K 900K
TQFP	100	158K	
LQFP	100 144 208	158К 158К 433К	
QFP	120 144 160 176 208 240	158K 158K 228K 228K 358K 545K	
HQFP	208 240 256		
PBGA	256 352	545K	807K
FBGA	112 144 168 176 192 224 288	192K 228K 228K 289K 433K	— 807К

CE81 Series

Features

High Integration : Maximum of 34,000,000 BCs Technology : 0.18 µm Si-gate CMOS, 4- to 5-layer wiring Supply voltage : +1.8 V \pm 0.15 V (normal) to +1.1 V \pm 0.1 V Gate delay time : tpd = 12 ps (1.8V, Inverter, F/O = 1)Gate power consumption : 8nW/MHz/BC (1.1V, 2NAND, F/O = 1) Junction temperature range : -40 to +125 °C Output buffer cells with noise reduction circuits Inputs with on-chip input pull-up/pull-down resistors (33 k Ω typical) and bidirectional buffer cells. Buffer cells for crystal oscillation circuits. Special interfaces: P-CML, LVDS, PCI, AGP, USB, SDRAM-I/F, SSTL, and others IP macros: CPU, DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others Compiled cells (RAM/ROM/multipliers, and others) Configurable internal bus circuits Advanced for hardware/software co-design environment Short-term development using a timing driven layout tool Supports static timing sign-off Dramatically reducing the time for generating test vectors for timing verification and the simulation time. Hierarchical design environment for supporting large-scale circuits Supports optimization environment of power supply wire Simulation (before layout) considering of the input through rate and high resolution RC extraction base delay calculation (after layout), supporting development with minimized timing trouble after trial manufacture. Supports Signal Integrity Supports memory (RAM, ROM) SCAN Supports memory (RAM) BIST Supports boundary SCAN Supports At-Speed test on internal circuits Supports path delay test Supports transition delay test A variety of package options (TQFP, HQFP, EBGA, FBGA, TAB-BGA, LQFP) Note: Some items are in preparation.

Number of gates used in package

The table below lists the available package types and the reference number of gates used.

Package and pin count		0 2000K 4000K 6000K 8000K 10000K 12000K 14000K 16000K	
TAB-BGA	304 352 480 560 660 720	— 891К — 1254К — 1905К — 2689К — 3609К 9129К	
EBGA	576 660 672	5982K 9805K 7952K	
HQFP	208 240 256 304 304	<u> </u>	
TQFP	100 120	— 514K — 514K	
LQFP	144 176 208	722К 722К 1098К	
FBGA	288	4712K	

CE77 Series

Features

realures	
High integration : I	Maximum of 10,000,000 BCs
	0.25 μm Si-gate CMOS, 3- to 4-layer wiring
Supply voltage : ·	+2.5 V \pm 0.2 V (normal) to +1.5 V \pm 0.1 V
Junction temperature range :	
Gate delay time : 1	t _{pd} = 33 ps (2.5 V, Inverter, F/O = 1, No load)
	0.02 μ W/MHz (1.5 V, Inverter, F/O = 1, No load)
High-load driving capability :	I _{OL} = 2mA/4mA/8mA/12mA mixable.
Output buffer cells with noise re	
Inputs with on-chip input pull-u	p/pull-down resistors (25 k Ω typical) and bidirectional buffer cells.
Buffer cells for crystal oscillation	
	DS, T-LVTTL, SSTL, PCI, USB, GTL+, and others)
	DA, PLL, DAC, ADC, and others)
Compiled cells (RAM/ROM/FIF	
Configurable internal bus circu	
Advanced for hardware/software	
Short-term development using	
	nt for supporting large-scale circuits
Supports static timing sign-off	for concretion to stars for timing a wife stars and the simulation time
	for generating test vectors for timing verification and the simulation time.
	sidering the input through rate and detailed RC delay calculation (after layout),
Supports memory (RAM, ROM	ninimized timing trouble after trial manufacture.
Supports memory (RAM) BIST	
Supports boundary SCAN	
Supports path delay test	
	SQFP, LQFP, HQFP, FBGA, PBGA)
A variety of package options (c	

Note: Some items are in preparation.

Number of gates used in each package The table below lists the available package types and the reference number of gates used.

CE77 (V-Frame)

Package and pin count		0 1000k 2000k 3000k 4000k 5000k 6000k 7000k 8000k 9000k	Material
SQFP	176	274k	P
	208	803k	P
	240	965k	P
HQFP	208	1776k	P
	240	2276k	P
	256	1776k	P
	304	7128k	P
PBGA	256	618k	Р

P: Plastic

Package and pin count		0 500K 1000K 1500K 2000K 2500K 3000K 3500K 4000K 4500K 5000K	Material
LQFP	144 176 208 256	976 K 	P P P P
HQFP	208 240 256 304	1375 К 1609 К 2109 К 4538 К	P P P P
FBGA	144 176 224 288	461 К 646 К 1375 К 2109 К	P P P P
PBGA	256 352 420	1841 К 2678 К 3789 К	P P P

CE77 (T-Frame)

P: Plastic

CE71 Series

Features

Features	
High integration	: Maximum of 8,000,000 BCs
Technology	: 0.25 μm Si-gate CMOS, 3- to 4-layer metal wiring
Supply voltage	: +2.5 V \pm 0.2 V (normal) to +1.5 V \pm 0.1 V
	(5 V TTL interface is available if 5 V tolerant I/O is adopted. Some frames are under
• • • • •	development.)
Gate delay time	: t _{pd} = 29 ps (2.5 V, Inverter, F/O = 1, No load)
Gate power cons	
	ture range : -40 to +125°C
	capability : $I_{OL} = 2 \text{ mA/4 mA/8 mA/12 mA mixable.}$
	s with noise reduction circuits
	ip input pull-up/pull-down resistors (25 k Ω typical) and bidirectional buffer cells.
	ystal oscillation circuits.
	(P-CML, LVDS, SDRAM-I/F, SSTL, and others)
	Clite, FR40, F ² MC16LX, PCI, IEEE1394, USB, IrDA, PLL, ADC/DAC, and others)
	AM/ROM/multipliers, and others)
Configurable inte	
	dware/software co-design environment tools and logic synthesis tools and logic synthesis tools allows automatic optimization of the circuits using the floor plan
	Clock Driven Design Method (CDDM) clock tree synthesis tools using the floor plan information are
	ing the floor plan information in the pre-layout stage would eliminate the problems of setup after lay-
	lems for hold, significantly reducing the time to market.
	ic timing sign off using the Synopsys CAD tool Prime Time. This contributes to the considerable
	required for test vector creation for timing verification and the simulation time.
	e layout) considering the input through rate and detailed RC delay calculation (after layout),
	opment with minimized timing trouble after trial manufacture.
	(RAM, ROM) SCAN
Supports memory	(RAM) BIST
Supports bounda	ry SCAN
A variety of packa	age options (SQFP, LQFP, HQFP, PBGA, EBGA, TAB-BGA, FBGA)

Note: Some items are in preparation.

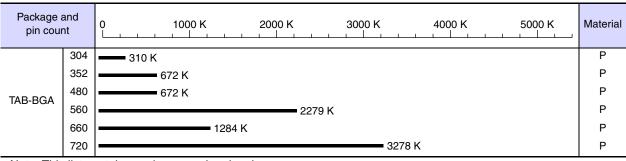
Number of gates used in each package

The table below lists the available package types and the reference number of gates used. CE71 (J-Frame)

Package and pin count		0 1000 K 2000 K 3000 K 4000 K 5000 K	Material
	176	203 K	Р
SQFP	208	592 K	Р
	240		Р
	208	1313 K	Р
HQFP	240	1681 K	Р
	256	1313 K	Р
	304		Р
PBGA	256	457 K	
	352		Р
	420	1313 K	Р
EBGA	576	1986 K	Р
	660	5345 K	Р
	672	2673 K	Р

P: Plastic

CE71 (L-Frame)



Note: This list contains packages under planning. P: Plastic

CE71 (T-Frame)

Package and pin count		0 1000 K 2000 K 3000 K 4000 K 5000 K	Material
	144	341 K	Р
LQFP	176	477 K	Р
LQIT	208	1014 K	Р
	256	1358 K	Р
	208		Р
	240		Р
HQFP	256	1559 K	Р
	304		Р
	144	341 K	Р
FBGA	176	477 К	Р
FBGA	224	1014 K	Р
	288	1559 K	Р
PBGA	256	1358 K	Р
	352	1976 K	Р
	420		Р

Note: This list contains packages under planning.

P: Plastic

CE66 Series

Features

Γ	eatures	
	High integration	: Maximum of 1,138,000 BCs
	Technology	: 0.35 μm Si-gate, 3- to 4-layer metal wiring
	Supply voltage	: +3.3 V \pm 0.3 V (normal) to +2.0 V \pm 0.1 V
		+5.0 V \pm 10% (only for external interface; when internal requirements is 3.3 V) +3.3 V \pm 10% (only for external interface; when internal requirements is 3.3 to 2.0 V)
	Gate delay time	: t _{pd} = 98 ps (high-speed type, F/O = 2, standard load)
	Gate power consumption	: 0.29 μ W/MHz (F/O = 2, standard load)
	Junction temperature range	: - 40 to 125°C
	High-load driving capability	: I _{OL} = 2 mA/4mA/8mA/12mA/24mA mixable.
	Output buffer cells with noise	e reduction circuits
	On-chip input pull-up/pull-do	
	Buffer cells dedicated to cry	
	Configurable internal bus cir	
		//multipliers mountable; arbitrary words/bits configurable.
	tion, reducing turnaround tin	ethod (CDDM) based on the floor plan information minimizes post-layout circuit modifica-
		onsidering the input through rate and detailed RC delay calculation (after layout),
		h minimized timing trouble after trial manufacture.
		and SDRAM-I/F, and others)
	Analog PLL	, ,
	Analog circuits (ADC, DAC,	OPAMP and others)
	Macros for system ASICs (C	CPU core, CPU peripheral, operational macros, and others)
	Supports DFF scan test with	
	Supports memory (RAM/RC	
	Supports memory (RAM) BI	SI
	Supports boundary SCAN	

Number of gates used in each package The table below lists the available package types and the reference number of gates used. CE66 (P-frame)

Package and pin count		0 100K 200K 300K 400K 500K 600K 700K 800K 900K 1000K 110C	
TQFP	100		— 1138K
LQFP	100 144 176 208	939K	— 1138K — 1138K — 1138K
QFP	120 144 160 176 208 240 256		— 1138K — 1138K — 1138K — 1138K — 1138K — 1138K — 1138K — 1138K
HQFP	208 240 256 304		
PBGA	256 352		— 1138K — 1138K
FBGA	112 144 168 176 192 224 288	459K 459K 601K 939K	— 1138K — 1138K — 1138K

Note: This list contains packages under planning.

CE66 (S-frame)

Package and pin count		0 50K 100K 150K 200K 250K 300K 350K 400K 450K 500K 550K 600K
TQFP	100	112K
LQFP	100 144 208	112K 112K 311K
QFP	120 144 160 176 208 240	112К 112К 163К 163К 256К 390К
HQFP	208 240 256	256K 390K 390K
PBGA	256 352	390K 579K
FBGA	112 144 168 176 192 224 288	136К 163К 311К 163К 206К 311К 579К

CE61 Series

Features

reatures	
High Integration	: Maximum of 2,000,000 BCs
Technology	: 0. 35 μ m Si-gate 3-layer metal wiring/4-layer metal wiring
	(There are restrictions applicable frames)
Basic circuit (basic cell)	: 2-input NAND/2-input NOR gates
Supply voltage	: +3.3 V ± 0.3 V (normal) to +2.0 V ± 0.1 V
	High voltage tolerant transistor for I/O; interface provided for 5 V devices
	(Also requiring a 5 V power supply for interface with 5 V devices)
Gate delay time	: High-speed type, t _{pd} = 85 ps (2-input NAND, F/O = 2, standard load)
Junction temperature range	
High-load driving capability	: I _{OL} = 2 mA/4 mA/8 mA/12 mA/24 mA mixable.
Power consumption	: Reduced to 50% to 20% (over the CE51 Series)
Output buffer cells with nois	
On-chip input pull-up/pull-do	
Buffer cells for crystal oscilla	
Configurable internal bus ci	
	and ROM available. Compilable bit/word configuration
,	t design technique (CDDM) employed to minimize circuit modification after layout, reduc-
ing TAT	analdering the input through rate and detailed DC delay calculation (after layout)
	onsidering the input through rate and detailed RC delay calculation (after layout), minimized timing trouble after trial manufacture.
	ices [P-CML (200 MHz transmission), LVDS (250 MHz transmission), and SDRAM I/F,
PCI,5 V tolerant, USB, IEEE	
PLL circuits	- 1204]
Analog circuits (ADC, DAC)	
	CPU core and CPU peripheral and operational macros, and others)
	/DC) using DFF scan with MUX
	BIST, RAM SCAN and ROM SCAN
Supports the Boundary SC	
Now under preparation on f	or a narrow-pitch pad technology and high-pin count BGA packages to be added to the
current lineup	
Variety of package options t	o optimize any gate size

Number of gates used in each package)

The table below lists the available package types and the reference number of gates used."

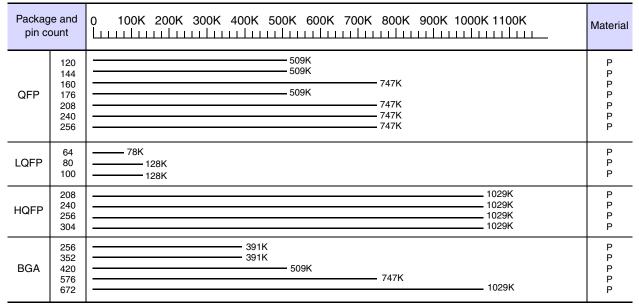
CE61 (F10 to F80)

Package and pin count		0 100K 200K 300K 400K 500K 600K 700K 800K 900K 1000K1100K1200K1300K	Material
QFP	64 80 100 120 144 160 176 208 208 240 240 256 256 304	86K 86K 86K 86K 981K 1317K 1317K	Р
LQFP	64 80 100	86K 86K 86K	P P P
HQFP	208 240 256 304	981K 1317K 981K 1317K	P P P P
BGA	256 352 420	593K981K	P P P
PGA	256 299 361 401		с с с

P: Plastic C: Ceramic

Note: This list contains packages under planning.

CE61 (E7 to E71)



P : Plastic

CG61 Series (Analog PLL embedment is possible in some frames)

Features

: 1,560,000 BCs
: 0. 35 μ m Si-gate CMOS, 3-layer metal wiring
: 2-input NAND/2-input NOR gates
: +3.3 V ± 0.3 V (normal) to +2.0 V ± 0.1 V
(5 V TTL interface is possible when 5 V tolerant I/Os are used.)
: t _{pd} = 85 ps (3.3 V, 2-input NAND, F/O = 2, standard load)
: 0.24 μ W/MHz (2.0 V, 2-input NAND, F/O = 2, standard load)
ge :0 to +100 °C
ty : I _{OL} = 2 mA/4 mA/8 mA/12 mA/24 mA mixable
pise reduction circuits
down resistors (Typ. 50 k Ω <at 3.3="" v="">)</at>
illation circuits
circuits
nbedded. Compilable bit/word configuration
bedded in CG61P only.
t design technique (CDDM) employed to minimize circuit modification after layout, reducing TAT
considering the input through rate and detailed RC delay calculation (after layout),
h minimized timing trouble after trial manufacture.
faces (T-LVTTL, P-CML, LVDS, SDRAM I/F)
scan with MUX
1 BIST and RAM SCAN

Number of gates used in each package The table below lists the available package types and the reference number of gates used.

CG 61 (The frame which cannot use Analog PLL)

Package and pin count		0 100K 200K 300K 400K 500K 600K 700K 800K 900K	Material
LQFP	120	222К	P
	144	222К	P
QFP	240	222K	P
	256	395K	P
HQFP	208 240 256 304	580K 802K	P P P P

P: plastic

Note: This list contains packages under planning.

CG 61P (The frame which can use Analog PLL)

Pack ar pin c	nd	0 20K 40K 60K 80K 100K 120K 140K 160K 180K 200K	Material
LQFP	120 144	16K 88K 188K	P P P P P
	176 208		P P
QFP	240 256		P P
BCC	48 64	88K 88K	P P

P: plastic

CG47 Series

Features

i caluics		
High integration	: Maximum 55,000 BCs (on chip)	
Technology	: 0.65 μm Si-gate CMOS, 2-layer metal wiring	
Gate delay time	: 300ps (power type 2-input NAND, standard load)	
Supply voltage	: [Single power supply] $+5 V \pm 5\%$ (normal), $+3.3 V \pm 0.3 V$ (normal)	
	[Dual power supply] Internal domain: $+3.3 V \pm 0.3 V$, $+5 V \pm 5\%$ (cannot be mixed)	
	$I/O: +3.3 V \pm 0.3 V, +5 V \pm 5\%$ (can be mixed)	
Interface enabled betweer	dual power sources	
Low power consumption e	nabled by operating internal supply voltage at 3.3V.	
Delay time estimation by d	etailed time equations	
Detailed time equations ca	in be used for the estimation of delay time closer to that of actual devices.	
Buffer cells for crystal osci	lations circuits	
Supports separate low free	quency (32 kHz), and high frequency (1 to 40MHz) buffers, and oscillator stop function.	
Supports output open drai	n cell and input fail safe cells	
Compiled cells include sin	ale port BAM, dual port BAM, and EIEO memory	

Compiled cells include single port RAM, dual port RAM, and FIFO memory.

Note: The type of the RAM that can be used is specified depending on the internal power supply when the RAM is a single-port RAM.

HISCAN (scan circuit automatic generation function)

HISCAN is supported with single power supply, but dual power supply specifications and HISCAN are mutually exclusive.

Simple interface

CAD-to-CAD interface uses special language for logic data (FLDL) and test data (FTDL).

Integrated development tools

Number of gates used in each package

The table below lists the available package types and the reference number of gates used.

Package and pin count		0 5K 10K 15K 20K 25K 30K 35K 40K 45K 50K
SSOP	30	— 2К
LQFP	48 64 80 100 120 144 176 208	11K 21K 33K 33K 33K 33K 33K 33K
QFP	64 80 100 240	21K 21K 21K 21K 33K
BCC	48 64 80	21K 31K 31K

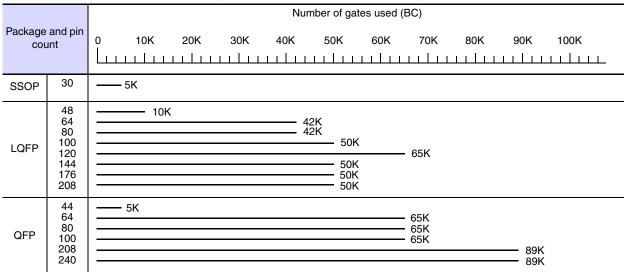
Sea-of-Gate Type CMOS Gate Arrays

CG46 Series

Features

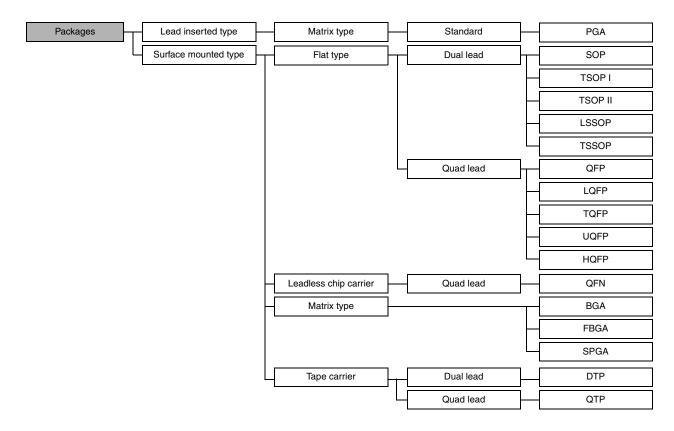
Caluico	
High integration	: Maximum 198,084 BCs (on chip)
Technology	: 0.65 μm Si-gate CMOS, 2-layer metal wiring
Basic circuit (basic cell)	: 2-input NAND/2-input NOR gates
Input level	: TTL/CMOS level mixable
Supply voltage	: +5 V ± 5% (normal)
	+3.3 V \pm 0.3 V (optional)
Gate delay time	: Standard gate tpd = 360 ps (2-input NAND, standard load)
	Power gate tpd = 300 ps (2-input NAND, standard load)
Operating temperature	: 0 to +70°C
High-load driving capability	: I _{OL} = 3.2 mA/8 mA/12 mA/24 mA mixable
Output buffer cells with nois	e reduction circuits
On-chip input pull-up/pull-do	own resistors (Typ. 50 kΩ)
Buffer cells for crystal oscilla	ations circuits
Configurable internal bus cir	rcuits
RAM and FIFO memory allo	owing arbitrary bit/word configuration
Clock skew reduction layout	design technique (CDDM) employed to minimize circuit modification after layout, reduc-
ing the period of time for dev	
Delailed RC delay calculation	on minimized timing trouble after trial manufacture.
Supports ATG (Automatic Te	est Generation) based on scan design
Supports HISCAN (automat	ic scan generation)
Simplified interface: CAD-to	-CAD interface uses special language for logic data (FLDL) and test data (FTDL).
Integrated development tool	S

Number of gates used in each package The table below lists the available package types and the reference number of gates used.



■ Package Line-up

The packages are classified as follows, according to form, material, and the mounting methods for which they are suited.



Name of package	Description	Lead pitch (mm)
PGA	Pin Grid Array Package	1.27/2.54
SOP	SOP Small Outline Package (straight lead) Small Outline L-Leaded Package	
SOL ^{*2}	Small Outline L-Leaded Package (JEDEC*1)	1.27
SSOP	Shrink Small Outline L-Leaded Package	0.65/0.80/1.00
TSOP (I)	Thin Small Outline L-Leaded Package (I)	0.50/0.55/0.60
TSOP (II)	Thin Small Outline L-Leaded Package (II)	0.50/0.80/1.00/1.27
SON	Small Outline Non-Leaded Package	0.50/1.00
QFP	Quad Flat Package (straight lead) Quad Flat L-Leaded Package	0.40/0.50/0.65/0.80/1.00
LQFP*2	Low-Profile Quad Flat L-Leaded Package	0.40/0.50/0.65/0.80
TQFP	Thin Quad Flat L-Leaded Package	0.40/0.50
HQFP	QFP with Heat Sink	0.40/0.50/0.65
LCC ^{*2}	Leadless Chip Carrier	1.010/1.07
QFN	Quad Flat Non-Leaded Package	1.016/1.27
BGA	Ball Grid Array	1.27/1.0
FBGA	Fine pitch Ball Grid Array	0.8/0.75/0.65/0.5
DTP	Dual Tape Carrier Package	—
QTP	Quad Tape Carrier Package	—

*1: Joint Electron Device Engineering Council

*2: Package name used by Fujitsu Microelectronics

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